TPD8S300 USB Type-C™ポート・プロテクタ: V_{BUS}への短絡過電圧およびIEC ESD保護

1 特長

- 4チャネルのV_{BUS}への短絡過電圧保護(CC1、CC2、SBU1、SBU2): 24V_{DC}許容
- 8チャネルのIEC 61000-4-2 ESD保護(CC1、CC2、SBU1、SBU2、DP_T、DM_T、DP_B、DM_B)
- CC1、CC2過電圧保護FET: V_{CONN}電力に600mAを供給可能
- CCデッド・バッテリ抵抗の内蔵により、モバイル・デバイスでのデッド・バッテリ状況に対応
- 3mm×3mmのWQFNパッケージ

2 アプリケーション

- ラップトップPC
- タブレット
- スマートフォン
- モニタおよびTV
- ドッキング・ステーション

3 概要

TPD8S300はシングル・チップのUSB Type-Cポート保護ソリューションで、20VのV_{BUS}への短絡過電圧およびIEC ESD保護を行います。

USB Type-Cコネクタのリリース以降、USB Type-C用でありながら、USB Type-Cの仕様を満たしていない多くの製品やアクセサリがリリースされました。このような例の1つは、USB Type-C電力供給アダプタで、V_{BUS}ライン上にしか20Vを印加しないものです。USB Type-Cに関する別の懸念として、小さなコネクタのピンが互いに近接して配置されているため、コネクタの機械的なねじれや水平方向のずれによってピン間が短絡することがあります。これによって、20V V_{BUS}がCCおよびSBUピンと短絡する恐れがあります。また、Type-Cコネクタのピンが互いに近接して配置されていることから、破片や湿気により20V V_{BUS}ピンがCCおよびSBUピンと短絡する危険も高まっています。

これらの理想的でない機器や機械的事象が存在するため、CCおよびSBUピンは5V以下の電圧でのみ動作するにもかかわらず、20V許容にする必要があります。TPD8S300はCCおよびSBUピンの過電圧保護を行うため、通常の動作に影響することなくCCおよびSBUピンを20V許容にできます。このデバイスは、SBUおよびCCラインと直列に高電圧FETを配置します。OVPスレッショルドを超える電圧がこれらのラインに検出された場合、高電圧スイッチが開き、システムの他の部分を、コネクタに存在している高電圧の状況から絶縁します。

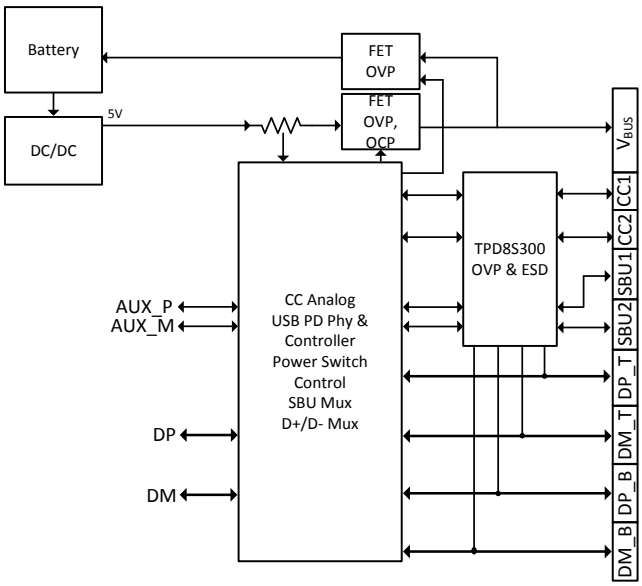
最後に、ほとんどのシステムでは外部ピンについてIEC 61000-4-2システム・レベルのESD保護が必要です。TPD8S300にはCC1、CC2、SBU1、SBU2、DP_T (上側のD+)、DM_T (上側のD–)、DP_B (下側のD+)、DM_B (下側のD–)ピンのIEC 61000-4-2 ESD保護が内蔵されているため、コネクタの外部に高電圧TVSダイオードを配置する必要はありません。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
TPD8S300	WQFN (20)	3.00mm×3.00mm

(1) 提供されているすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。

アプリケーション図



Copyright © 2016, Texas Instruments Incorporated

英語版のTI製品についての情報を翻訳したこの資料は、製品の概要を確認する目的で便宜的に提供しているものです。該当する正式な英語版の最新情報は、www.ti.comで閲覧でき、その内容が常に優先されます。TIでは翻訳の正確性および妥当性につきましては一切保証いたしません。実際の設計などの前には、必ず最新版の英語版をご参照くださいますようお願いいたします。

目次

1 特長 ... 1
2 アプリケーション ... 1
3 概要 ... 1
4 改訂履歴 ... 2
5 **Device Comparison Table** ... 3
6 **Pin Configuration and Functions** ... 3
7 **Specifications** ... 5
7.1 Absolute Maximum Ratings ... 5
7.2 ESD Ratings—JEDEC Specification ... 5
7.3 ESD Ratings—IEC Specification ... 5
7.4 Recommended Operating Conditions ... 5
7.5 Thermal Information ... 6
7.6 Electrical Characteristics ... 6
7.7 Timing Requirements ... 9
7.8 Typical Characteristics ... 10
8 **Detailed Description** ... 15
8.1 Overview ... 15
8.2 Functional Block Diagram ... 16
8.3 Feature Description ... 16
8.4 Device Functional Modes ... 19
9 **Application and Implementation** ... 20
9.1 Application Information ... 20
9.2 Typical Application ... 20
10 **Power Supply Recommendations** ... 25
11 **Layout** ... 26
11.1 Layout Guidelines ... 26
11.2 Layout Example ... 26
12 デバイスおよびドキュメントのサポート ... 27
12.1 ドキュメントのサポート ... 27
12.2 ドキュメントの更新通知を受け取る方法 ... 27
12.3 コミュニティ・リソース ... 27
12.4 商標 ... 27
12.5 静電気放電に関する注意事項 ... 27
12.6 用語集 ... 27
13 メカニカル、パッケージ、および注文情報 ... 27

4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision A (September 2016) から **Revision B** に変更	**Page**
• データシートの最初の公開リリース	1

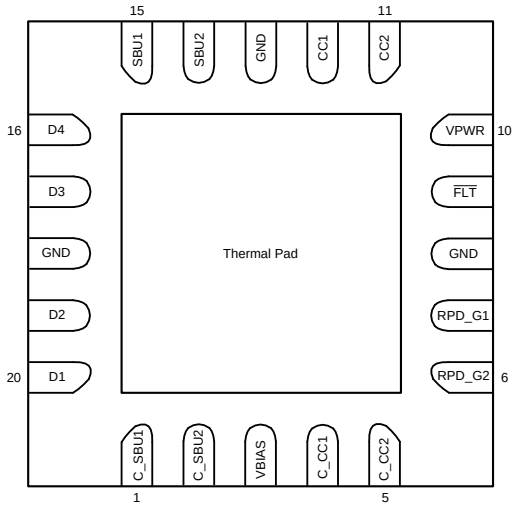
Copyright © 2016, Texas Instruments Incorporated

5 Device Comparison Table

Part Number	Over Voltage Protected Channels	IEC 61000-4-2 ESD Protected Channels
TPD6S300	4-Ch (CC1, CC2, SBU1, SBU2)	6-Ch (CC1, CC2, SBU1, SBU2, DP, DM)
TPD8S300	4-Ch (CC1, CC2, SBU1, SBU2)	8-Ch (CC1, CC2, SBU1, SBU2, DP_T, DM_T, DP_B, DM_B)

6 Pin Configuration and Functions

RUK Package
20 Pin WQFN
Top View



Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	C_SBU1	I/O	Connector side of the SBU1 OVP FET. Connect to either SBU pin of the USB Type-C connector
2	C_SBU2	I/O	Connector side of the SBU2 OVP FET. Connect to either SBU pin of the USB Type-C connector
3	VBIAS	Power	Pin for ESD support capacitor. Place a 0.1-µF capacitor on this pin to ground
4	C_CC1	I/O	Connector side of the CC1 OVP FET. Connect to either CC pin of the USB Type-C connector
5	C_CC2	I/O	Connector side of the CC2 OVP FET. Connect to either CC pin of the USB Type-C connector
6	RPD_G2	I/O	Short to C_CC2 if dead battery resistors are needed. If dead battery resistors are not needed, short pin to GND
7	RPD_G1	I/O	Short to C_CC1 if dead battery resistors are needed. If dead battery resistors are not needed, short pin to GND
8	GND	GND	Ground
9	$\overline{FLT}$	O	Open drain for fault reporting
10	V_{PWR}	Power	2.7-V-3.6-V power supply
11	CC2	I/O	System side of the CC2 OVP FET. Connect to either CC pin of the CC/PD controller
12	CC1	I/O	System side of the CC1 OVP FET. Connect to either CC pin of the CC/PD controller
13	GND	GND	Ground

Copyright © 2016, Texas Instruments Incorporated

Pin Functions (continued)

PIN		TYPE	DESCRIPTION
NO.	NAME		
14	SBU2	I/O	System side of the SBU2 OVP FET. Connect to either SBU pin of the SBU MUX
15	SBU1	I/O	System side of the SBU1 OVP FET. Connect to either SBU pin of the SBU MUX
16	D4	I/O	USB2.0 IEC ESD protection. Connect to any of the USB2.0 pins of the USB Type-C connector
17	D3	I/O	USB2.0 IEC ESD protection. Connect to any of the USB2.0 pins of the USB Type-C connector
18	GND	GND	Ground
19	D2	I/O	USB2.0 IEC ESD protection. Connect to any of the USB2.0 pins of the USB Type-C connector
20	D1	I/O	USB2.0 IEC ESD protection. Connect to any of the USB2.0 pins of the USB Type-C connector
—	Thermal Pad	GND	Internally connected to GND. Used as a heatsink. Connect to the PCB GND plane

Copyright © 2016, Texas Instruments Incorporated

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)[1]

			MIN	MAX	UNIT
V_I	Input voltage	V_{PWR}	–0.3	4	V
		RPD_G1, RPD_G2	–0.3	24	V
V_O	Output voltage	$\overline{FLT}$	–0.3	6	V
		VBIAS	–0.3	24	V
V_{IO}	I/O voltage	D1, D2, D3, D4	–0.3	6	V
		CC1, CC2, SBU1, SBU2	–0.3	6	V
		C_CC1, C_CC2, C_SBU1, C_SBU2	–0.3	24	V
T_A	Operating free air temperature		–40	85	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings—JEDEC Specification

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Pins listed as ±2000 V may actually have higher performance.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Pins listed as ±500 V may actually have higher performance.

7.3 ESD Ratings—IEC Specification

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge[1]	IEC 61000-4-2, C_CC1, C_CC2, D1, D2, D3, D4	Contact discharge	±8000	V
			Air-gap discharge	±15000	
		IEC 61000-4-2, C_SBU1, C_SBU2	Contact discharge	±6000	
			Air-gap discharge	±15000	

(1) Tested on the TPD8S300 EVM connected to the TPS65982 EVM.

7.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_I	Input voltage	V_{PWR}	2.7	3.3	3.6	V
		RPD_G1, RPD_G2	0		5.5	V
V_O	Output voltage	$\overline{FLT}$ pull-up resistor power rail	2.7		5.5	V
V_{IO}	I/O voltage	D1, D2, D3, D4	–0.3		5.5	V
		CC1, CC2, C_CC1, C_CC2	0		5.5	V
		SBU1, SBU2, C_SBU1, C_SBU2	0		4.3	V
I_{VCONN}	V_{CONN} current	Current flowing into CC1/2 and flowing out of C_CC1/2, VCCx – VC_CCx ≤ 250 mV			600	mA
I_{VCONN}	V_{CONN} current	Current flowing into CC1/2 and flowing out of C_CC1/2, T_J ≤ 105°C			1.25	A

Copyright © 2016, Texas Instruments Incorporated

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
External components (1)	$\overline{FLT}$ pull-up resistance	1.7		300	kΩ
	VBIAS capacitance (2)		0.1		µF
	V_{PWR} capacitance	0.3	1		µF

(1) For recommended values for capacitors and resistors, the typical values assume a component placed on the board near the pin. Minimum and maximum values listed are inclusive of manufacturing tolerances, voltage derating, board capacitance, and temperature variation. The effective value presented must be within the minimum and maximums listed in the table.
(2) The VBIAS pin requires a minimum 35-V_{DC} rated capacitor. A 50-V_{DC} rated capacitor is recommended to reduce capacitance derating. See the *VBIAS Capacitor Selection* section for more information on selecting the VBIAS capacitor.

7.5 Thermal Information

THERMAL METRIC (1)		TPD8S300 RUK (WQFN) 20 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	45.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	48.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	17.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	17.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	3.7	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CC OVP Switches						
R_{ON}	On resistance of CC OVP FETs, T_J ≤ 85°C	CCx = 5.5 V		278	392	mΩ
	On resistance of CC OVP FETs, T_J ≤ 105°C	CCx = 5.5 V		278	415	mΩ
R_{ONFLAT}	On resistance flatness	Sweep CCx voltage between 0 V and 1.2 V			5	mΩ
C_{ON_CC}	Equivalent on capacitance	Capacitance from C_CCx or CCx to GND when device is powered. VC_CCx/VCCx = 0 V to 1.2 V , f = 400 kHz	60	74	120	pF
RD_DB	Dead battery pull-down resistance (only present when device is unpowered). Effective resistance of R_D and FET in series	V_C_CCx = 2.6 V	4.1	5.1	6.1	kΩ
VTH_DB	Threshold voltage of the pulldown FET in series with RD during dead battery	I_CC = 80 µA	0.5	0.9	1.2	V
V_{OVPCC}	OVP threshold on CC pins	Place 5.5 V on C_CCx. Step up C_CCx until the $\overline{FLT}$ pin is asserted	5.75	6	6.2	V
V_{OVPCC_HYS}	Hysteresis on CC OVP	Place 6.5 V on C_CCx. Step down the voltage on C_CCx until the $\overline{FLT}$ pin is deasserted. Measure difference between rising and falling OVP threshold for CC		50		mV

Copyright © 2016, Texas Instruments Incorporated

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BW_{ON}	On bandwidth single ended (–3 dB)	Measure the –3-dB bandwidth from C_CCx to CCx. Single ended measurement, 50-Ω system. Vcm = 0.1 V to 1.2 V		100		MHz
V_{STBUS_CC}	Short-to-VBUS tolerance on the CC pins	Hot-Plug C_CCx with a 1 meter USB Type C Cable, place a 30-Ω load on CCx			24	V
$V_{STBUS_CC_CLAMP}$	Short-to-VBUS system-side clamping voltage on the CC pins (CCx)	Hot-Plug C_CCx with a 1 meter USB Type C Cable. Hot-Plug voltage C_CCx = 24 V. VPWR = 3.3 V. Place a 30-Ω load on CCx		8		V
SBU OVP Switches						
R_{ON}	On resistance of SBU OVP FETs	SBUx = 3.6 V. –40°C ≤ T_J ≤ +85°C		4	6.5	Ω
R_{ONFLAT}	On resistance flatness	Sweep SBUx voltage between 0 V and 3.6 V. –40°C ≤ T_J ≤ +85°C		0.7	1.5	Ω
C_{ON_SBU}	Equivalent on capacitance	Capacitance from SBUx or C_SBUx to GND when device is powered. Measure at VC_SBUx/VSBUx = 0.3 V to 3.6 V		6		pF
V_{OVPSBU}	OVP threshold on SBU pins	Place 3.6 V on C_SBUx. Step up C_SBUx until the $\overline{FLT}$ pin is asserted	4.35	4.5	4.7	V
V_{OVPSBU_HYS}	Hysteresis on SBU OVP	Place 5 V on C_CCx. Step down the voltage on C_CCx until the $\overline{FLT}$ pin is deasserted. Measure difference between rising and falling OVP threshold for C_SBUx		50		mV
BW_{ON}	On bandwidth single ended (–3 dB)	Measure the –3-dB bandwidth from C_SBUx to SBUx. Single ended measurement, 50-Ω system. Vcm = 0.1 V to 3.6 V		1000		MHz
X_{TALK}	Crosstalk	Measure crosstalk at f = 1 MHz from SBU1 to C_SBU2 or SBU2 to C_SBU1. Vcm1 = 3.6 V, Vcm2 = 0.3 V. Be sure to terminate open sides to 50 Ω		–80		dB
V_{STBUS_SBU}	Short-to-VBUS tolerance on the SBU pins	Hot-Plug C_SBUx with a 1 meter USB Type C Cable. Put a 150-nF capacitor in series with a 40-Ω resistor to GND on SBUx			24	V
$V_{STBUS_SBU_CLAMP}$	Short-to-VBUS system-side clamping voltage on the SBU pins (SBUx)	Hot-Plug C_SBUx with a 1 meter USB Type C Cable. Hot-Plug voltage C_SBUx = 24 V. VPWR = 3.3 V. Put a 100-nF capacitor in series with a 40-Ω resistor to GND on SBUx		8		V
Power Supply and Leakage Currents						
V_{PWR_UVLO}	V_{PWR} under voltage lockout	Place 1 V on VPWR and raise voltage until SBU or CC FETs turnon	2.1	2.3	2.5	V
$V_{PWR_UVLO_HYS}$	V_{PWR} UVLO hysteresis	Place 3 V on VPWR and lower voltage until SBU or CC FETs turnoff; measure difference between rising and falling UVLO to calculate hysteresis	100	150	200	mV

Copyright © 2016, Texas Instruments Incorporated

Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{VPWR}	V_{PWR} supply current	VPWR = 3.3 V (typical), VPWR = 3.6 V (maximum). –40°C ≤ T_J ≤ +85°C.		90	120	µA
I_{CC_LEAK}	Leakage current for CC pins when device is powered	VPWR = 3.3 V, VC_CCx = 3.6 V, CCx pins are floating, measure leakage into C_CCx pins. Result must be same if CCx side is biased and C_CCx is left floating.			5	µA
I_{SBU_LEAK}	Leakage current for SBU pins when device is powered	VPWR = 3.3 V, VC_SBUx = 3.6 V, SBUx pins are floating, measure leakge into C_SBUx pins. Result must be same if SBUx side is biased and C_SBUx is left floating. –40°C ≤ T_J ≤ 85°C.			3	µA
$I_{C_CC_LEAK_OVP}$	Leakage current for CC pins when device is in OVP	VPWR = 0 V or 3.3 V, VC_CCx = 24 V, CCx pins are set to 0 V, measure leakage into C_CCx pins			1200	µA
$I_{C_SBU_LEAK_OVP}$	Leakage current for SBU pins when device is in OVP	VPWR = 0 V or 3.3 V, VC_SBUx = 24 V, SBUx pins are set to 0 V, measure leakage into C_SBUx pins			400	µA
$I_{CC_LEAK_OVP}$	Leakage current for CC pins when device is in OVP	VPWR = 0 V or 3.3 V, VC_CCx = 24 V, CCx pins are set to 0 V, measure leakage out of CCx pins			30	µA
$I_{SBU_LEAK_OVP}$	Leakage current for SBU pins when device is in OVP	VPWR = 0 V or 3.3 V, VC_SBUx = 24 V, SBUx pins are set to 0 V, measure leakage out of SBUx pins	–1		1	µA
I_{Dx_LEAK}	Leakage current for Dx pins	V_Dx = 3.6 V, measure leakage into Dx pins			1	µA
$\overline{FLT}$ Pin						
V_{OL}	Low-level output voltage	IOL = 3 mA. Measure the voltage at the $\overline{FLT}$ pin			0.4	V
Over Temperature Protection						
T_{SD_RISING}	The rising over-temperature protection shutdown threshold		150	175		°C
$T_{SD_FALLING}$	The falling over-temperature protection shutdown threshold		130	140		°C
T_{SD_HYST}	The over-temperature protection shutdown threshold hysteresis			35		°C
Dx ESD Protection						
V_{RWM_POS}	Reverse stand-off voltage from Dx to GND	Dx to GND. I_{DX} ≤ 1 µA			5.5	V
V_{RWM_NEG}	Reverse stand-off voltage from GND to Dx	GND to Dx			0	V
V_{BR_POS}	Break-down voltage from Dx to GND	Dx to GND. I_{BR} = 1 mA	7			V
V_{BR_NEG}	Break-down voltage from GND to Dx	GND to Dx. I_{BR} = 8 mA	0.6			V
C_{IO}	Dx to GND or GND to Dx	f = 1 MHz, VIO = 2.5 V		1.7		pF
ΔC_{IO}	Differential capacitance between two Dx pins	f = 1 MHz, VIO = 2.5 V		0.02		pF
R_{DYN}	Dynamic on-resistance Dx IEC clamps	Dx to GND or GND to Dx		0.4		Ω

Copyright © 2016, Texas Instruments Incorporated

7.7 Timing Requirements

		MIN	NOM	MAX	UNIT
Power-On and Off Timings					
t_{ON}	Time from crossing rising VPWR UVLO until CC and SBU OVP FETs are on			3.5	ms
dV_{PWR_OFF}/dt	Minimum slew rate allowed to guarantee CC and SBU FETs turnoff during a power off	–0.5			V/µs
Over Voltage Protection					
$t_{OVP_RESPONSE_CC}$	OVP response time on the CC pins. Time from OVP asserted until OVP FETs turnoff		70		ns
$t_{OVP_RESPONSE_SBU}$	OVP response time on the SBU pins. Time from OVP asserted until OVP FETs turnoff		80		ns
$t_{OVP_RECOVERY_CC_1}$	OVP recovery time on the CC pins. Once an OVP has occurred, the minimum time duration until the CC FETs turn back on. OVP must be removed for CC FETs to turn back on	21	29	39	ms
$t_{OVP_RECOVERY_SBU_1}$	OVP recovery time on the SBU pins. Once an OVP has occurred, the minimum time duration until the SBU FETs turn back on. OVP must be removed for SBU FETs to turn back on	21	29	39	ms
$t_{OVP_RECOVERY_CC_2}$	OVP recovery time on the CC pins. Time from OVP removal until CC FET turns back on, if device has been in OVP > 40 ms		0.5		ms
$t_{OVP_RECOVERY_SBU_2}$	OVP recovery time on the SBU pins. Time from OVP removal until SBU FET turns back on, if device has been in OVP > 40 ms		0.5		ms
$t_{OVP_FLT_ASSERTION}$	Time from OVP asserted to $\overline{FLT}$ assertion		20		µs
$t_{OVP_FLT_DEASSERTION}$	Time from CC FET turnon after an OVP to $\overline{FLT}$ deassertion		5		ms

Copyright © 2016, Texas Instruments Incorporated

7.8 Typical Characteristics

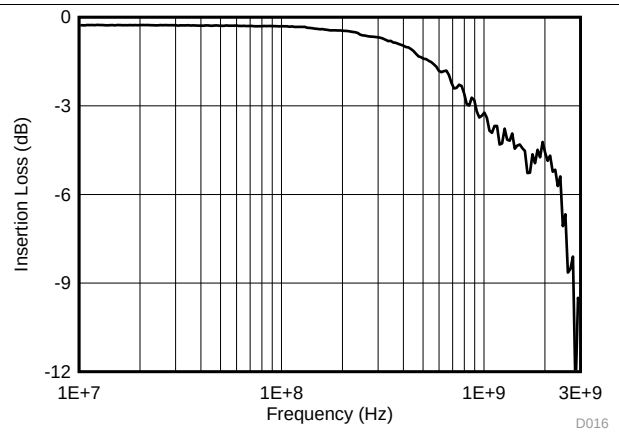


図 1. SBU S21 BW

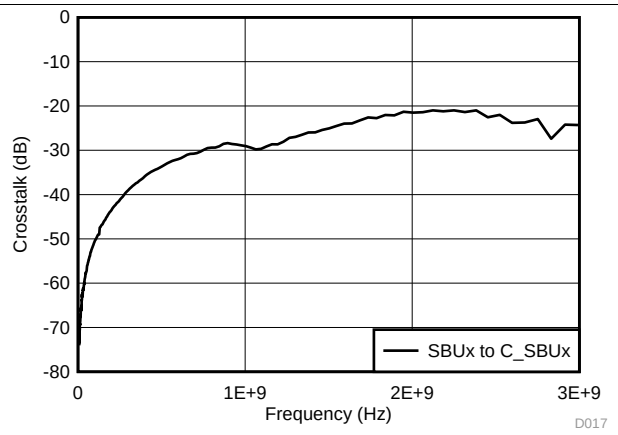


図 2. SBU Crosstalk

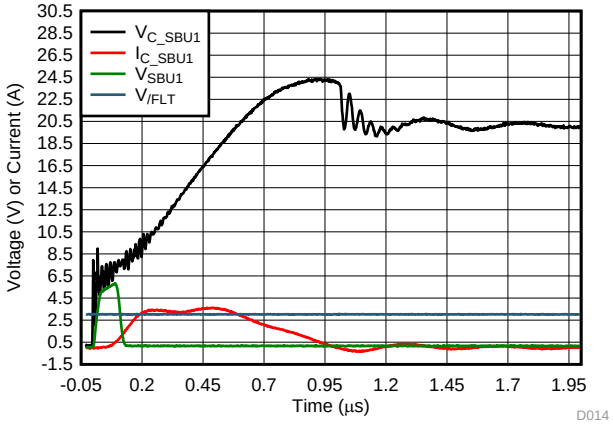


図 3. SBU Short-to-V_{BUS} 20 V

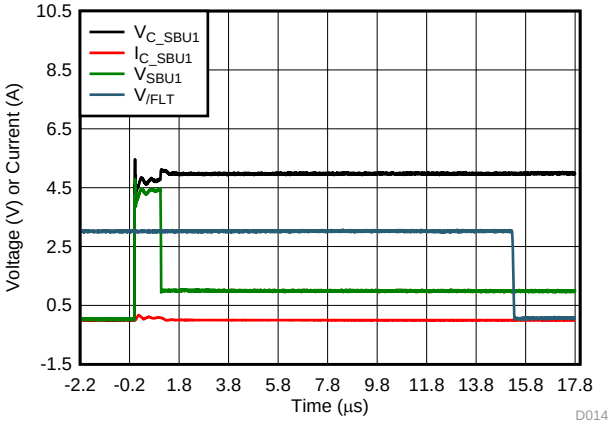


図 4. SBU Short-to-V_{BUS} 5 V

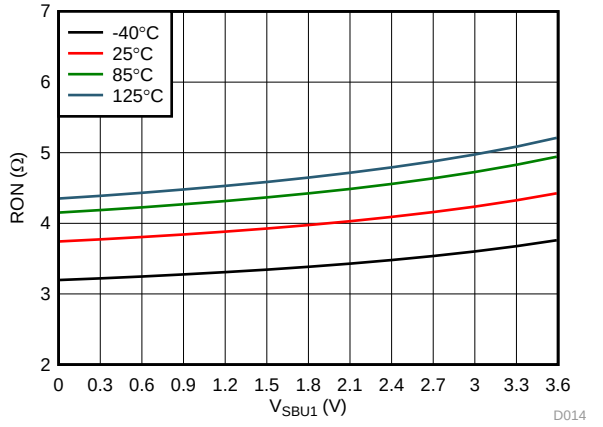


図 5. SBU R_{ON} Flatness

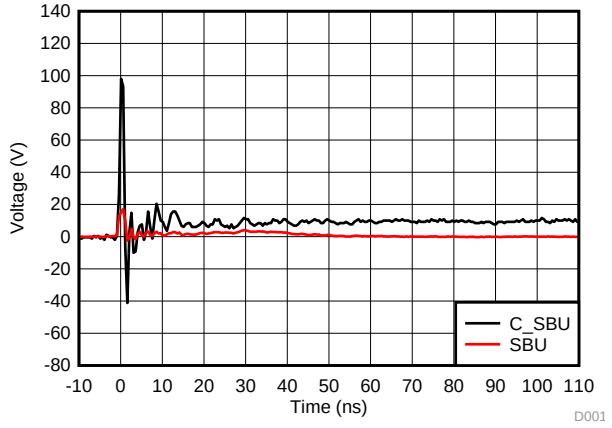


図 6. SBU IEC 61000-4-2 4-kV Response Waveform

Copyright © 2016, Texas Instruments Incorporated

Typical Characteristics (continued)

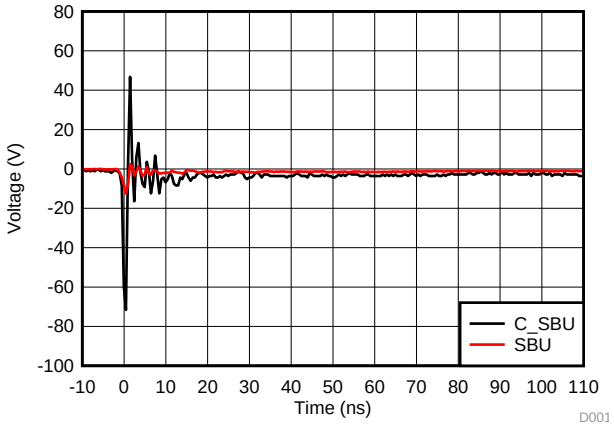


図 7. SBU IEC 61000-4-2 –4-kV Response Waveform

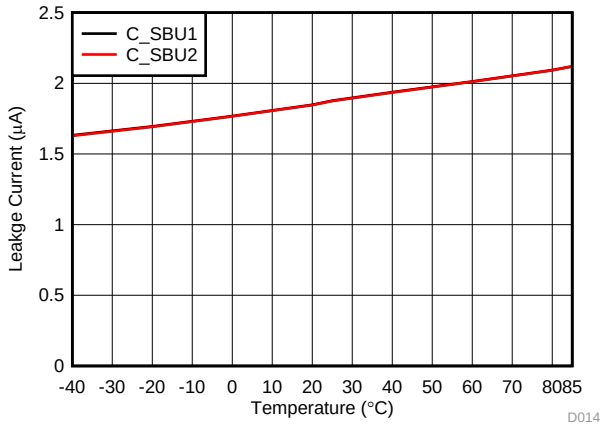


図 8. SBU Path Leakage Current vs Ambient Temperature at 3.6 V

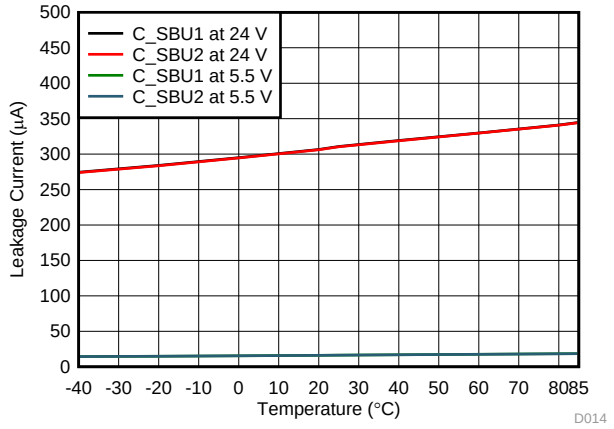


図 9. C_SBU OVP Leakage Current vs Ambient Temperature at 5.5 V and 24 V

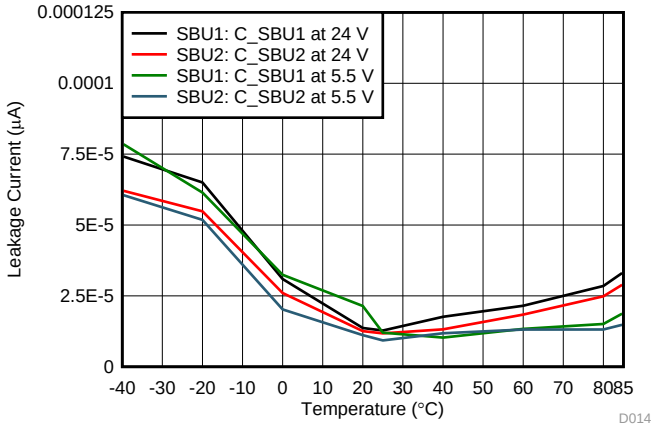


図 10. SBU OVP Leakage Current vs Ambient Temperature at 5.5 V and 24 V

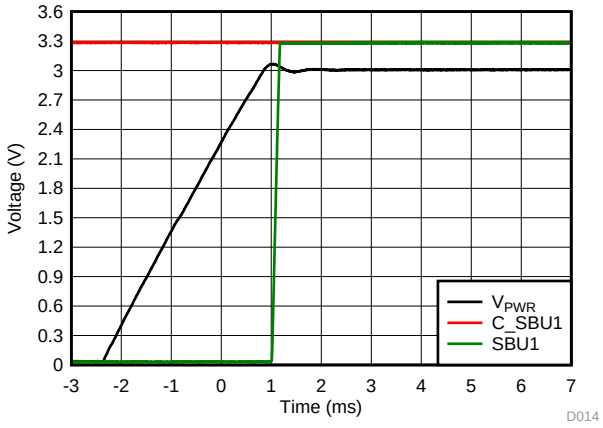


図 11. SBU FET Turnon Timing

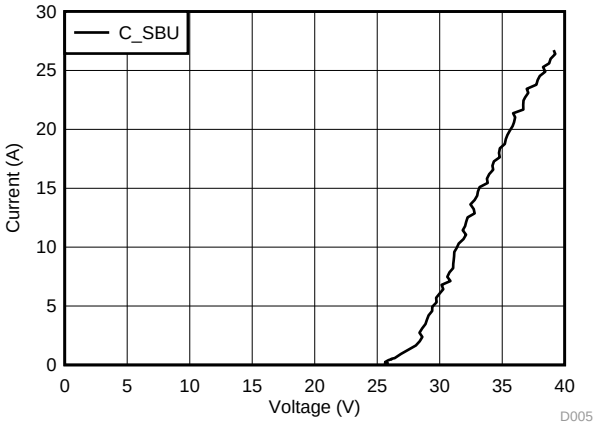


図 12. C_SBU TLP Curve Unpowered

Typical Characteristics (continued)

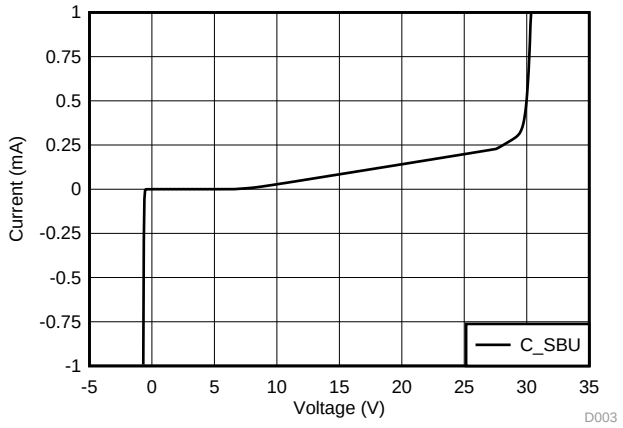


図 13. SBU IV Curve

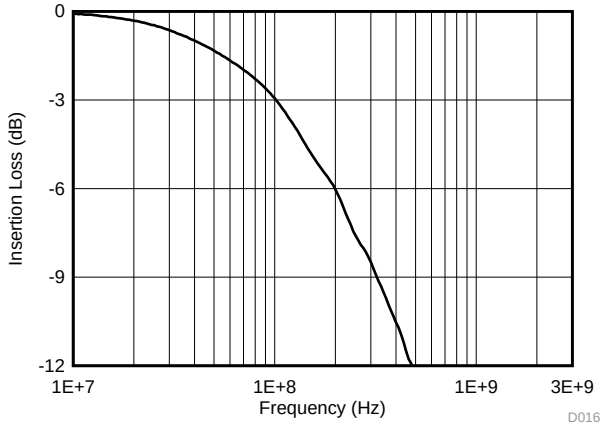


図 14. CC S21 BW

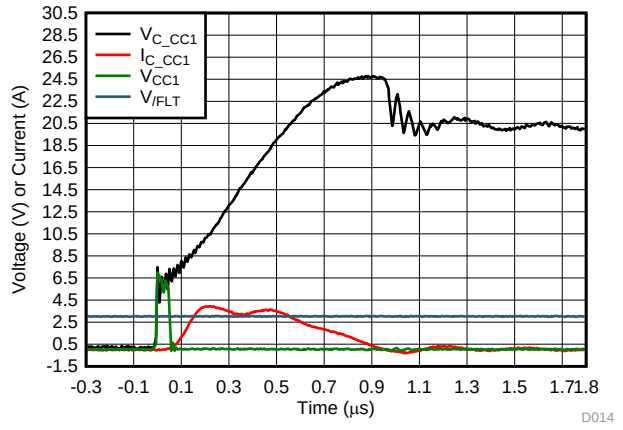


図 15. CC Short-to-V_{BUS} 20 V

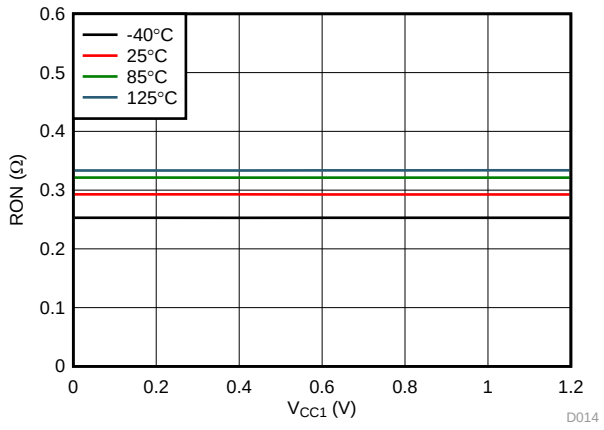


図 16. CC R_{ON} Flatness

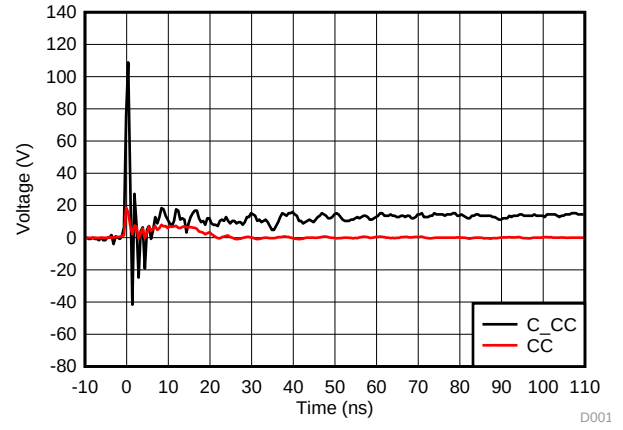


図 17. CC IEC 61000-4-2 8-kV Response Waveform

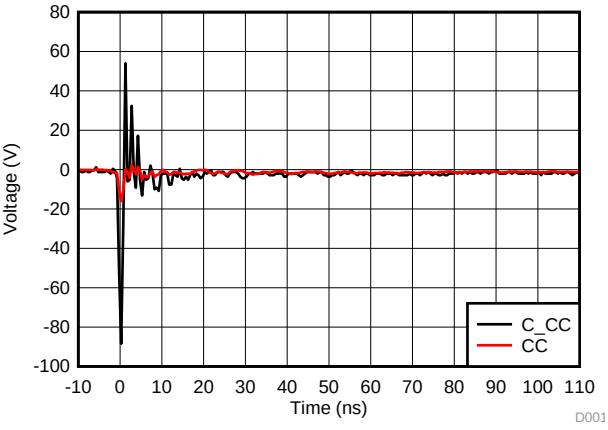


図 18. CC IEC 61000-4-2 –8-kV Response Waveform

Copyright © 2016, Texas Instruments Incorporated

Typical Characteristics (continued)

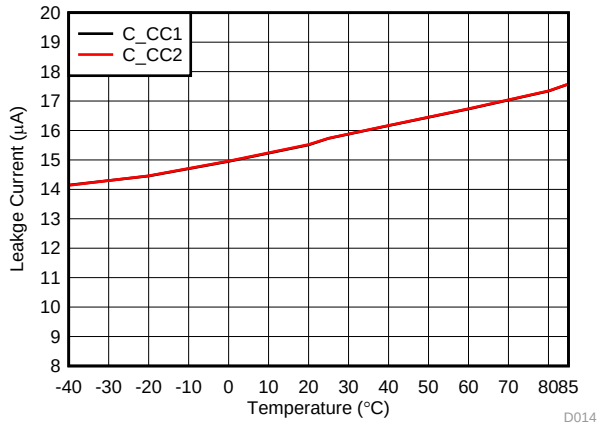


図 19. C_CC Path Leakage Current vs Ambient Temperature at C_CC = 5.5 V

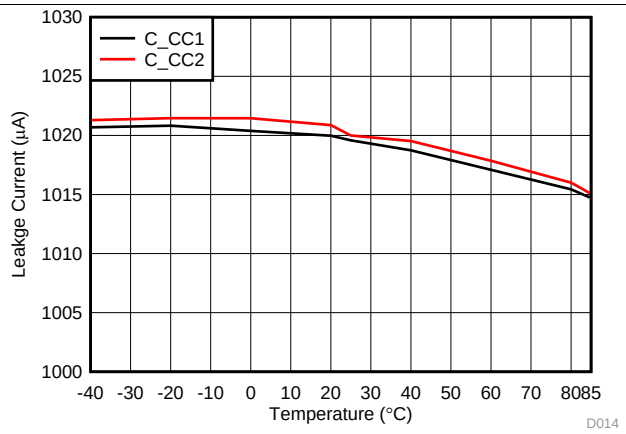


図 20. C_CC OVP Leakage Current vs Ambient Temperature at C_CC = 24 V

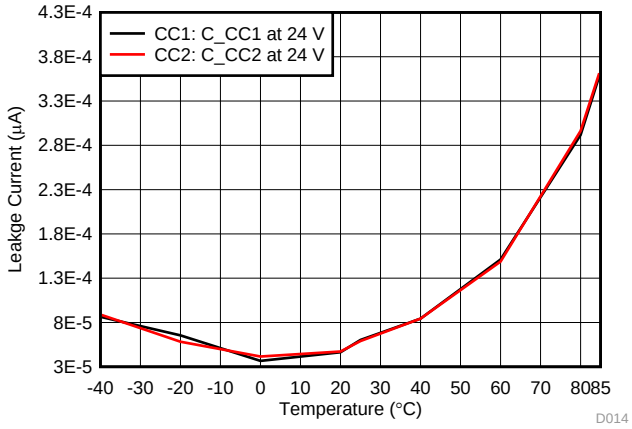


図 21. CC OVP Leakage Current vs Ambient Temperature at C_CC = 24 V

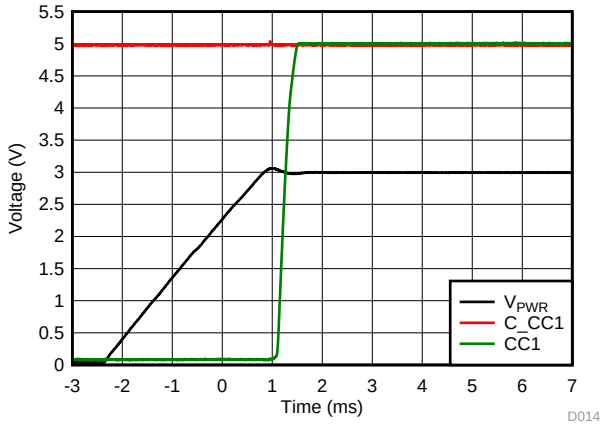


図 22. CC FET Turnon Timing

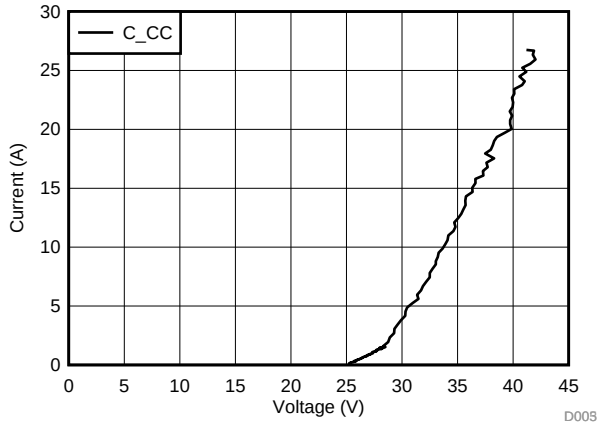


図 23. C_CC TLP Curve Unpowered

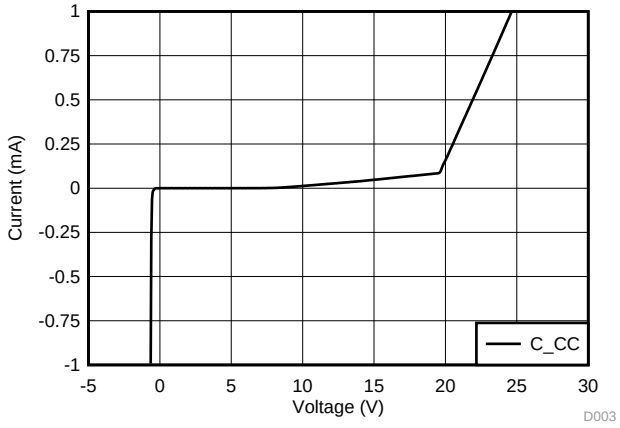


図 24. C_CC IV Curve

Typical Characteristics (continued)

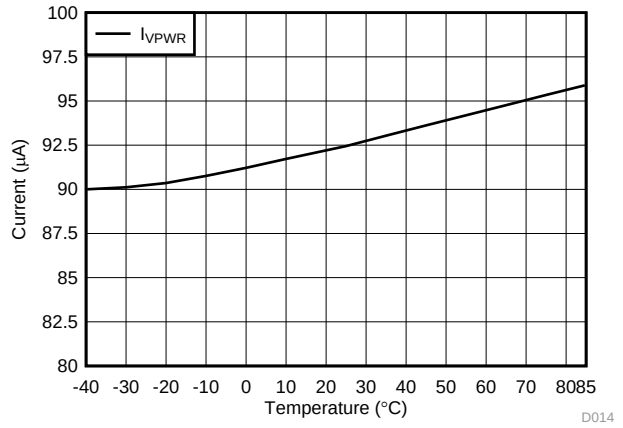


図 25. V_{PWR} Supply Leakage vs Ambient Temperature at 3.6 V

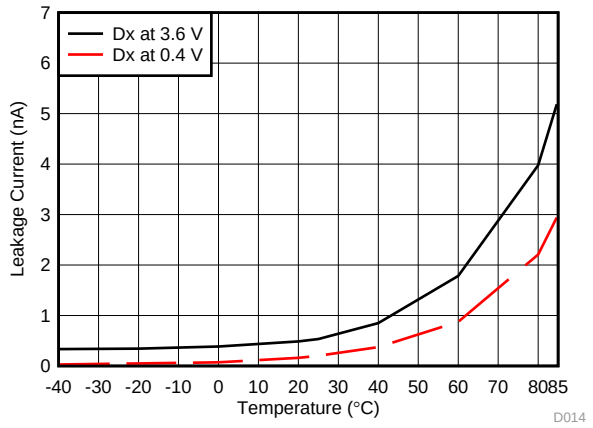


図 26. Dx Leakage Current vs Ambient Temperature at 0.4 V and 3.6 V

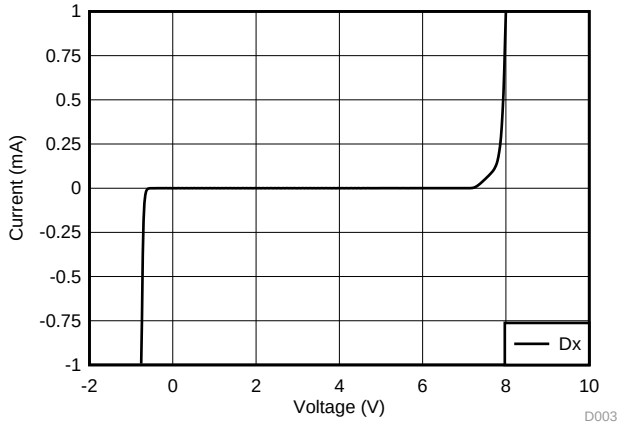


図 27. Dx IV Curve

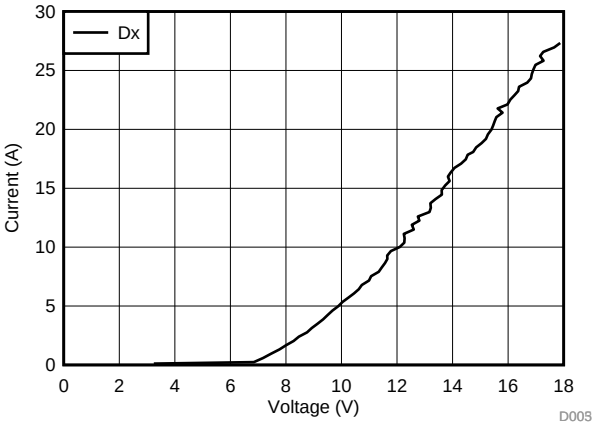


図 28. Dx TLP Curve

Copyright © 2016, Texas Instruments Incorporated

8 Detailed Description

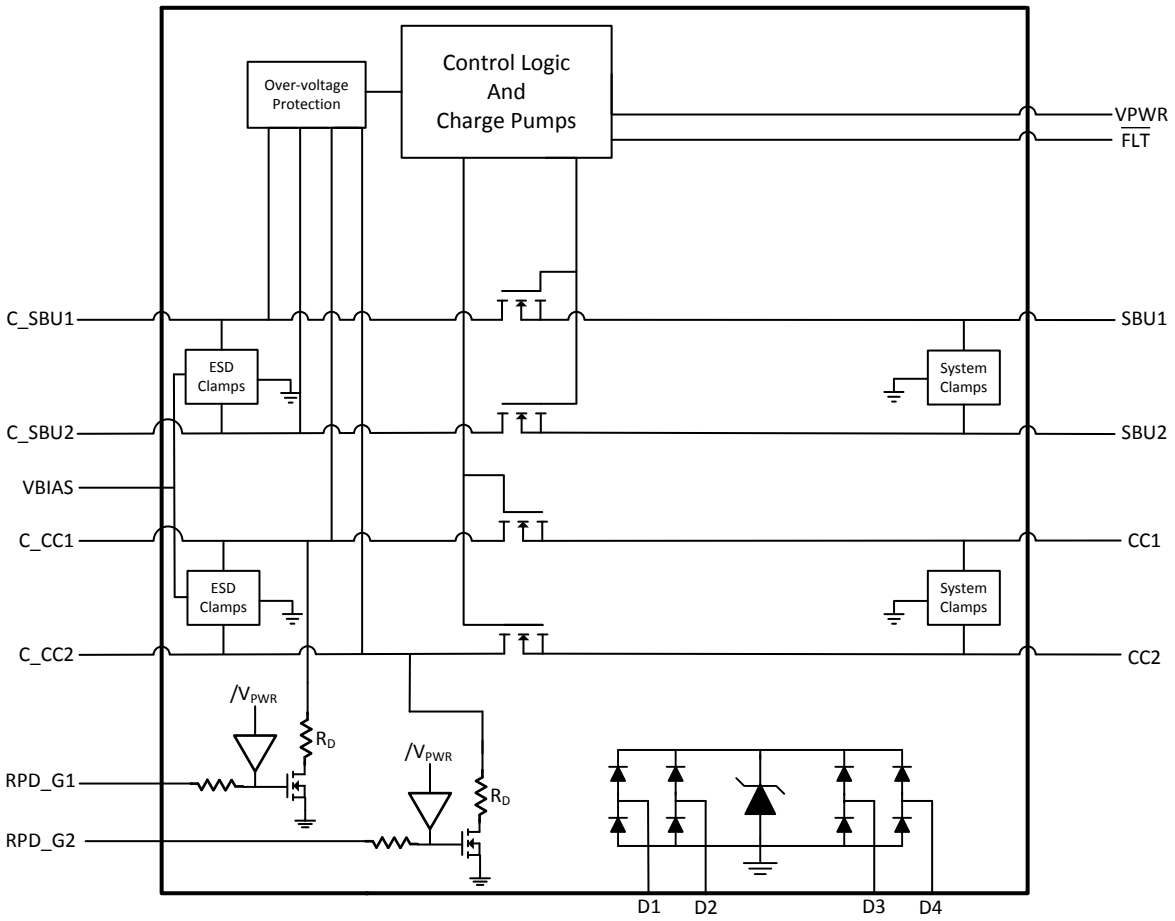
8.1 Overview

The TPD8S300 is a single chip USB Type-C port protection solution that provides 20-V Short-to-V_{BUS} overvoltage and IEC ESD protection. Due to the small pin pitch of the USB Type-C connector and non-compliant USB Type-C cables and accessories, the V_{BUS} pins can get shorted to the CC and SBU pins inside the USB Type-C connector. Because of this short-to-V_{BUS} event, the CC and SBU pins need to be 20-V tolerant, to support protection on the full USB PD voltage range. Even if a device does not support 20-V operation on V_{BUS}, non complaint adaptors can start out with 20-V V_{BUS} condition, making it necessary for any USB Type-C device to support 20 V protection. The TPD8S300 integrates four channels of 20-V Short-to-V_{BUS} overvoltage protection for the CC1, CC2, SBU1, and SBU2 pins of the USB Type-C connector.

Additionally, IEC 61000-4-2 system level ESD protection is required in order to protect a USB Type-C port from ESD strikes generated by end product users. The TPD8S300 integrates eight channels of IEC61000-4-2 ESD protection for the CC1, CC2, SBU1, SBU2, DP_T (Top side D+), DM_T (Top Side D–), DP_B (Bottom Side D+), and DM_B (Bottom Side D–) pins of the USB Type-C connector. This means IEC ESD protection is provided for all of the low-speed pins on the USB Type-C connector in a single chip in the TPD8S300. Additionally, high-voltage IEC ESD protection that is 22-V DC tolerant is required for the CC and SBU lines in order to simultaneously support IEC ESD and Short-to-V_{BUS} protection; there are not many discrete market solutions that can provide this kind of protection. This high-voltage IEC ESD diode is what the TPD8S300 integrates, specifically designed to guarantee it works in conjunction with the overvoltage protection FETs inside the device. This sort of solution is very hard to generate with discrete components.

Copyright © 2016, Texas Instruments Incorporated

8.2 Functional Block Diagram



Copyright © 2016, Texas Instruments Incorporated

8.3 Feature Description

8.3.1 4-Channels of Short-to-V_{BUS} Overvoltage Protection (CC1, CC2, SBU1, SBU2 Pins): 24-V_{DC} Tolerant

The TPD8S300 provides 4-channels of Short-to-V_{BUS} Overvoltage Protection for the CC1, CC2, SBU1, and SBU2 pins of the USB Type-C connector. The TPD8S300 is able to handle 24-V_{DC} on its C_CC1, C_CC2, C_SBU1, and C_SBU2 pins. This is necessary because according to the USB PD specification, with V_{BUS} set for 20-V operation, the V_{BUS} voltage is allowed to legally swing up to 21 V, and 21.5 V on voltage transitions from a different USB PD V_{BUS} voltage. The TPD8S300 builds in tolerance up to 24-V_{BUS} to provide margin above this 21.5 V specification to be able to support USB PD adaptors that may break the USB PD specification.

When a short-to-V_{BUS} event occurs, ringing happens due to the RLC elements in the hot-plug event. With very low resistance in this RLC circuit, ringing up to twice the settling voltage can appear on the connector. More than 2x ringing can be generated if any capacitor on the line derates in capacitance value during the short-to-V_{BUS} event. This means that more than 44 V could be seen on a USB Type-C pin during a Short-to-V_{BUS} event. The TPD8S300 has built in circuit protection to handle this ringing. The diode clamps used for IEC ESD protection also clamp the ringing voltage during the short-to-V_{BUS} event to limit the peak ringing to around 30 V. Additionally, the overvoltage protection FETs integrated inside the TPD8S300 are 30-V tolerant, therefore being capable of supporting the high-voltage ringing waveform that is experienced during the short-to-V_{BUS} event. The well designed combination of voltage clamps and 30-V tolerant OVP FETs insures the TPD8S300 can handle Short-to-V_{BUS} hot-plug events with hot-plug voltages as high as 24-V_{DC}.

Copyright © 2016, Texas Instruments Incorporated

Feature Description (continued)

The TPD8S300 has an extremely fast turnoff time of 70 ns typical. Furthermore, additional voltage clamps are placed after the OVP FET on the system side (CC1, CC2, SBU1, SBU2) pins of the TPD8S300, to further limit the voltage and current that is exposed to the USB Type-C CC/PD controller during the 70 ns interval while the OVP FET is turning off. The combination of connector side voltage clamps, OVP FETs with extremely fast turnoff time, and system side voltage clamps all work together to insure the level of stress seen on a CC1, CC2, SBU1, or SBU2 pin during a short-to-V_{BUS} event is less than or equal to an HBM event. This is done by design, as any USB Type-C CC/PD controller will have built in HBM ESD protection.

図 29 is an example of the TPD8S300 successfully protecting the TPS65982, the world's first fully integrated, full-featured USB Type-C and PD controller.

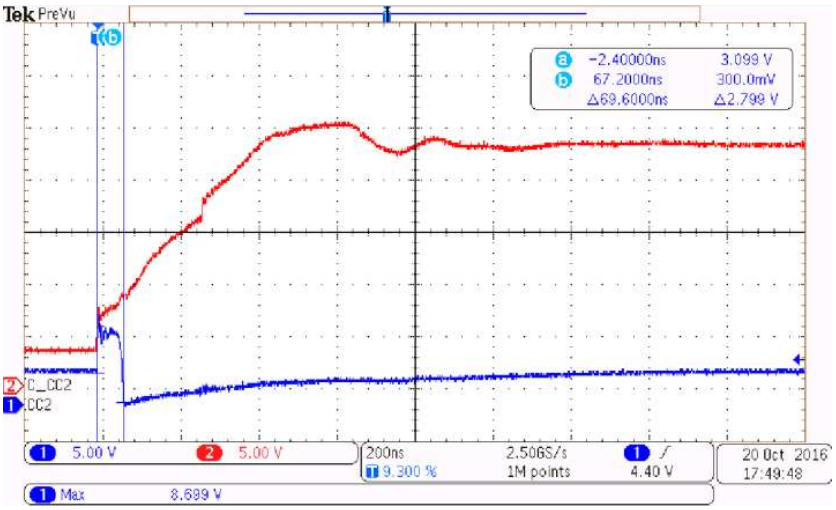


図 29. TPD8S300 Protecting the TPS65982 During a Short-to-V_{BUS} Event

8.3.2 8-Channels of IEC 61000-4-2 ESD Protection (CC1, CC2, SBU1, SBU2, DP_T, DM_T, DP_B, DM_B Pins)

The TPD8S300 integrates 8-Channels of IEC 61000-4-2 system level ESD protection for the CC1, CC2, SBU1, SBU2, DP_T (Top side D+), DM_T (Top Side D–), DP_B (Bottom Side D+), and DM_B (Bottom Side D–) pins. USB Type-C ports on end-products need system level IEC ESD protection in order to provide adequate protection for the ESD events that the connector can be exposed to from end users. The TPD8S300 integrates IEC ESD protection for all of the low-speed pins on the USB Type-C connector in a single chip. Also note, that while the RPD_Gx pins are not individually rated for IEC ESD, when they are shorted to the C_CCx pins, the C_CCx pins provide protection for both the C_CCx pins and the RPD_Gx pins. Additionally, high-voltage IEC ESD protection that is 24-V DC tolerant is required for the CC and SBU lines in order to simultaneously support IEC ESD and Short-to-V_{BUS} protection; there are not many discrete market solutions that can provide this kind of protection. The TPD8S300 integrates this type of high-voltage ESD protection so a system designer can meet both IEC ESD and Short-to-V_{BUS} protection requirements in a single device.

8.3.3 CC1, CC2 Overvoltage Protection FETs 600 mA Capable for Passing VCONN Power

The CC pins on the USB Type-C connector serve many functions; one of the functions is to be a provider of power to active cables. Active cables are required when desiring to pass greater than 3 A of current on the V_{BUS} line or when the USB Type-C port uses the super-speed lines (TX1+, TX2–, RX1+, RX1–, TX2+, TX2–, RX2+, RX2–). When CC is configured to provide power, it is called VCONN. VCONN is a DC voltage source in the range of 3 V-5.5 V. If supporting VCONN, a VCONN provider must be able to provide 1 W of power to a cable; this translates into a current range of 200 mA to 333 mA (depending on your VCONN voltage level). Additionally, if operating in a USB PD alternate mode, greater power levels are allowed on the VCONN line.

Copyright © 2016, Texas Instruments Incorporated

Feature Description (continued)

When a USB Type-C port is configured for VCONN and using the TPD8S300, this VCONN current flows through the OVP FETs of the TPD8S300. Therefore, the TPD8S300 has been designed to handle these currents and have an RON low enough to provide a specification compliant VCONN voltage to the active cable. The TPD8S300 is designed to handle up to 600 mA of DC current to allow for alternate mode support in addition to the standard 1 W required by the USB Type-C specification.

8.3.4 CC Dead Battery Resistors Integrated for Handling the Dead Battery Use Case in Mobile Devices

An important feature of USB Type-C and USB PD is the ability for this connector to serve as the sole power source to mobile devices. With support up to 100 W, the USB Type-C connector supporting USB PD can be used to power a whole new range of mobile devices not previously possible with legacy USB connectors.

When the USB Type-C connector is the sole power supply for a battery powered device, the device must be able to charge from the USB Type-C connector even when its battery is dead. In order for a USB Type-C power adapter to supply power on V_{BUS}, RD pull-down resistors must be exposed on the CC pins. These RD resistors are typically included inside a USB Type-C CC/PD controller. However, when the TPD8S300 is used to protect the USB Type-C port, the OVP FETs inside the device isolates these RD resistors in the CC/PD controller when the mobile device has no power. This is because when the TPD8S300 has no power, the OVP FETs are turned off to guarantee overvoltage protection in a dead battery condition. Therefore, the TPD8S300 integrates high-voltage, dead battery RD pull-down resistors to allow dead battery charging simultaneously with high-voltage OVP protection.

If dead battery support is required, short the RPD_G1 pin to the C_CC1 pin, and short the RPD_G2 pin to the C_CC2 pin. This connects the dead battery resistors to the connector CC pins. When the TPD8S300 is unpowered, and the RP pull-up resistor is connected from a power adaptor, this RP pull-up resistor activates the RD resistor inside the TPD8S300. This enables V_{BUS} to be applied from the power adaptor even in a dead battery condition. Once power is restored back to the system and back to the TPD8S300 on its VPWR pin, the TPD8S300 removes its RD pull-down resistor and turn on its OVP FETs within 3.5 ms to guarantee the RD pull-down resistor inside the CC/PD Controller is exposed within 10 ms. This is by design, because if the RD pull-down resistor is not exposed within 10 ms, the power adaptor can legally interpret this behavior as a port disconnect and remove V_{BUS}.

If desiring to power the CC/PD controller during dead battery mode and if the CC/PD Controller is configured as a DRP, it is critical that the TPD8S300 be powered before or at the same time that the CC/PD controller is powered. It is also critical that when unpowered, the CC/PD controller also expose its dead battery resistors. When the TPD8S300 gets powered, it exposes the CC pins of the CC/PD controller within 3.5 ms. Once the TPD8S300 turns on, the RD pull-down resistors of the CC/PD controller must be present immediately, in order to guarantee the power adaptor connected to power the dead battery device keeps its V_{BUS} turned on. If the power adaptor sees any change to its CC voltage for more than 10 ms, it can disconnect V_{BUS}. This removes power from the device with its battery still not sufficiently charged, which consequently removes power from the CC/PD controller and the TPD8S300. Then the RD resistors of the TPD8S300 are exposed again, connect the power adaptor's V_{BUS} to start the cycle over. This creates an infinite loop, never or very slowly charging the mobile device.

If the CC/PD Controller is configured for DRP and has started its DRP toggle before the TPD8S300 turns on, this DRP toggle is unable to guarantee that the power adaptor does not disconnect from the port. Therefore, it is recommended if the CC/PD controller is configured for DRP, that its dead battery resistors be exposed as well, and that they remain exposed until the TPD8S300 turns on. This is typically accomplished by powering the TPD8S300 at the same time as the CC/PD controller when powering the CC/PD controller in dead battery operation.

If dead battery charging is not required in your application, connect the RPD_G1 and RPD_G2 pins to ground.

8.3.5 3-mm × 3-mm WQFN Package

The TPD8S300 comes in a small, 3-mm × 3-mm WQFN package, greatly reducing the size of implementing a similar protection solution discretely. The WQFN package allows support for a wider range of PCB designs. Additionally, the pin-out of the TPD8S300 was designed to optimize routing with the TPS6598x family of USB Type-C/PD controllers.

Copyright © 2016, Texas Instruments Incorporated

8.4 Device Functional Modes

表 1 describes all of the functional modes for the TPD8S300. The "X" in the below table are "do not care" conditions, meaning any value can be present within the absolute maximum ratings of the datasheet and maintain that functional mode. Also note the D1, D2, D3, D4 pins are not listed, because these pins have IEC ESD protection diodes that are always present, regardless of whether the device is powered and regardless of the conditions on any of the other pins.

表 1. Device Mode Table

Device Mode Table		Inputs					Outputs		
MODE		**VPWR**	**C_CCx**	**C_SBUx**	**RPD_Gx**	**T_J**	**$\overline{FLT}$**	**CC FETs**	**SBU FETs**
Normal Operating Conditions	Unpowered, no dead battery support	<UVLO	X	X	Grounded	X	High-Z	OFF	OFF
	Unpowered, dead battery support	<UVLO	X	X	Shorted to C_CCx	X	High-Z	OFF	OFF
	Powered on	>UVLO	<OVP	<OVP	X, forced OFF	<TSD	High-Z	ON	ON
Fault Conditions	Thermal shutdown	>UVLO	X	X	X, forced OFF	>TSD	Low (Fault Asserted)	OFF	OFF
	CC over voltage condition	>UVLO	>OVP	X	X, forced OFF	<TSD	Low (Fault Asserted)	OFF	OFF
	SBU over voltage condition	>UVLO	X	>OVP	X, forced OFF	<TSD	Low (Fault Asserted)	OFF	OFF

Copyright © 2016, Texas Instruments Incorporated

9 Application and Implementation

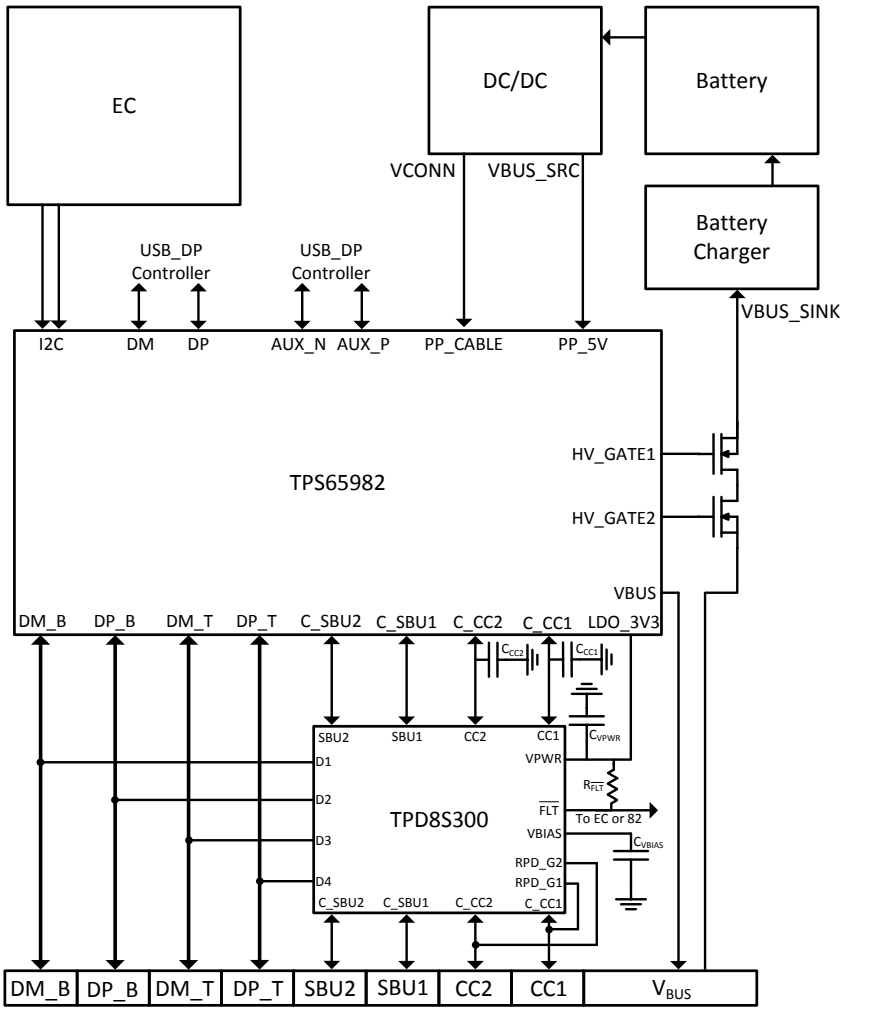
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPD8S300 provides 4-channels of Short-to-VBUS overvoltage protection for the CC1, CC2, SBU1, and SBU2 pins of the USB Type-C connector, and 8-channels of IEC ESD protection for the CC1, CC2, SBU1, SBU2, DP_T, DM_T, DP_B, DM_B pins of the USB Type-C connector. Care must be taken to insure that the TPD8S300 provides adequate system protection as well as insuring that proper system operation is maintained. The following application example explains how to properly design the TPD8S300 into a USB Type-C system.

9.2 Typical Application



Copyright © 2016, Texas Instruments Incorporated

図 30. TPD8S300 Typical Application Diagram

Copyright © 2016, Texas Instruments Incorporated

Typical Application (continued)

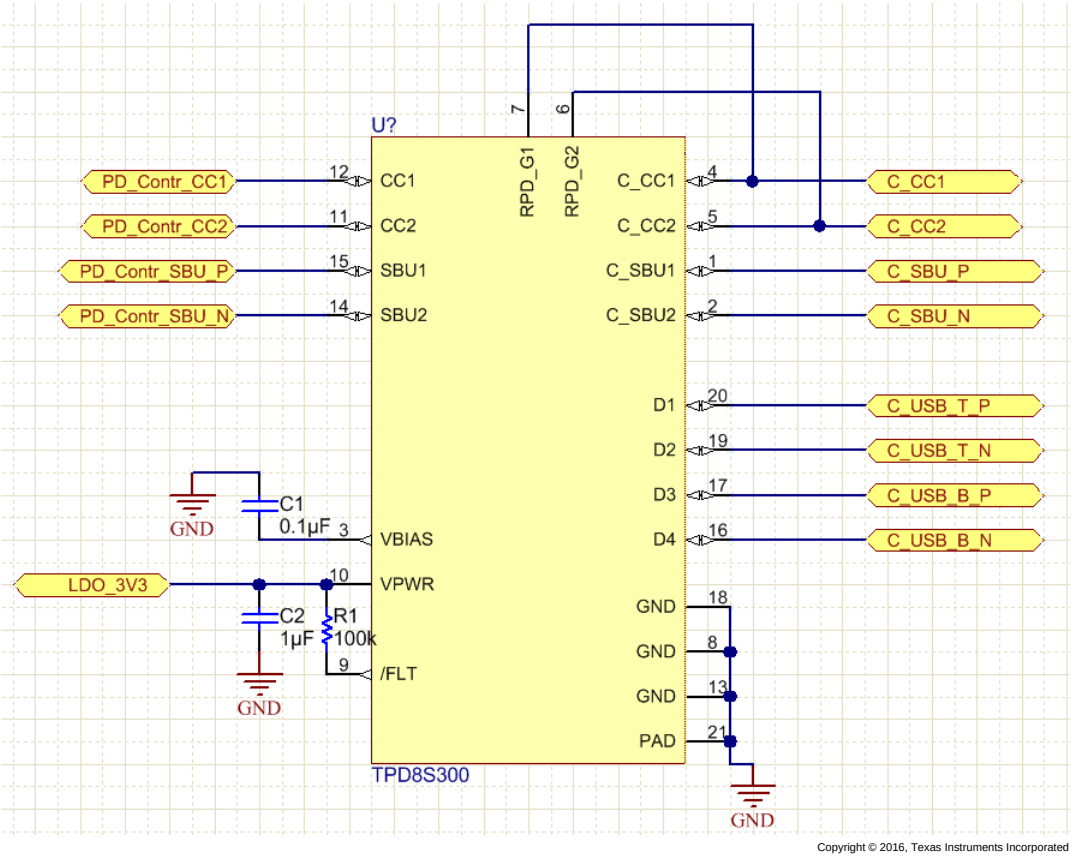


図 31. TPD8S300 Reference Schematic

9.2.1 Design Requirements

In this application example we study the protection requirements for a full-featured USB Type-C DRP Port, fully equipped with USB-PD, USB2.0, USB3.0, Display Port, and 100 W charging. The TPS65982 is used to easily enable a full-featured port with a single chip solution. In this application, all the pins of the USB Type-C connector are utilized. Both the CC and SBU pins are susceptible to shorting to the V_{BUS} pin. With 100 W charging, V_{BUS} operates at 20 V, requiring the CC and SBU pins to tolerate 20-V_{DC}. Additionally, the CC, SBU, and USB2.0 pins require IEC system level ESD protection. With these protection requirements present for the USB Type-C connector, the TPD8S300 is utilized. The TPD8S300 is a single chip solution that provides all the required protection for the low speed and USB2.0 pins in the USB Type-C connector.

表 2 shows the TPD8S300 desgin parameters.

表 2. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{BUS} nominal operating voltage	20 V
Short-to-V_{BUS} tolerance for the CC and SBU pins	24 V
VBIAS nominal capacitance	0.1 µF
Dead battery charging	100 W
Maximum ambient temperature requirement	85°C

9.2.2 Detailed Design Procedure

9.2.2.1 VBIAS Capacitor Selection

As noted in the *Recommended Operating Conditions* table, a minimum of 35-V_{BUS} rated capacitor is required for the VBIAS pin, and a 50-V_{BUS} capacitor is recommended. The VBIAS capacitor is in parallel with the central IEC diode clamp integrated inside the TPD8S300. A forward biased hiding diode connects the VBIAS pin to the C_CCx and C_SBUx pins. Therefore, when a Short-to-V_{BUS} event occurs at 20 V, 20-V_{BUS} minus a forward biased diode drop is exposed to the VBIAS pin. Additionally, during the short-to-V_{BUS} event, ringing can occur almost double the settling voltage of 20 V, allowing a potential 40 V to be exposed to the C_CCx and C_SBUx pins. However, the internal IEC clamps limits the voltage exposed to the C_CCx and C_SBUx pins to around 30 V. Therefore, at least 35-V_{BUS} capacitor is required to insure the VBIAS capacitor does not get destroyed during Short-to-V_{BUS} events.

A 50-V, X7R capacitor is recommended, however. This is to further improve the derating performance of the capacitors. When the voltage across a real capacitor is increased, its capacitance value derates. The more the capacitor derates, the greater than 2x ringing can occur in the short-to-V_{BUS} RLC circuit. 50-V X7R capacitors have great derating performance, allowing for the best short-to-V_{BUS} performance of the TPD8S300.

Additionally, the VBIAS capacitor helps pass IEC 61000-4-2 ESD strikes. The more capacitance present, the better the IEC performance. So the less the VBIAS capacitor derates, the better the IEC performance. 表 3 shows the real capacitors recommended to achieve the best performance with the TPD8S300.

表 3. Design Parameters

CAPACITOR SIZE	PART NUMBER
0402	CC0402KRX7R9BB104
0603	GRM188R71H104KA93D

9.2.2.2 Dead Battery Operation

For this application, we want to support 100-W dead battery operation; when the laptop is out of battery, we still want to charge the laptop at 20 V and 5 A. This means that the USB PD Controller must receive power in dead battery mode. The TPS65982 has its own built in LDO in order to supply the TPS65982 power from V_{BUS} in a dead battery condition. The TPS65982 can also provide power to its flash during this condition through its LDO_3V3 pin.

The TPD8S300s OVP FETs remain OFF when it is unpowered in order to insure in a dead battery situation proper protection is still provided to the PD controller in the system, in this case the TPS65982. However, when the OVP FETs are OFF, this isolates the TPS65982s dead battery resistors from the USB Type-C ports CC pins. A USB Type-C power adaptor must see the RD pull-down dead battery resistors on the CC pins or it does not provide power on V_{BUS}. Since the TPS65982s dead battery resistors are isolated from the USB Type-C connector's CC pins, The TPD8S300s built in dead battery resistors must be connected. Short the RPD_G1 pin to the C_CC1 pin, and short the RPD_G2 pin to the C_CC2 pin.

Once the power adaptor sees the TPD8S300s dead battery resistors, it applies 5 V on the V_{BUS} pin. This provides power to the TPS65982, turning the PD controller on, and allowing the battery to begin to charge. However, this application requires 100 W charging in dead battery mode, so V_{BUS} at 20 V and 5 A is required. USB PD negotiation is required to accomplish this, so the TPS65982 needs to be able to communicate on the CC pins. This means the TPD8S300 needs to be turned on in dead battery mode as well so the TPD65982s PD controller can be exposed to the CC lines. To accomplish this, it is critical that the TPD8S300 is powered by the TPS65982s internal LDO, the LDO_3V3 pin. This way, when the TPS65982 receives power on V_{BUS}, the TPD8S300 is turned on simultaneously.

It is critical that the TPS65982s dead battery resistors are also connected to its CC pins for dead battery operation. Short the TPS65982s RPD_G1 pin to its C_CC1 pin, and its RPD_G2 pin to its C_CC2 pin. It is critical that the TPS65982s dead battery resistors are present; once the TPD8S300 receives power, removes its dead battery resistors and turns on its OVP FETs, RD pull-down resistors must be present on the CC line in order to guarantee the power adaptor stays connected. If RD is not present and the voltage on CC changes for more than 10 ms, the power adaptor interprets this as a disconnect and remove V_{BUS}.

Also, it is important that the TPS65982s dead battery resistors are present so it properly boots up in dead battery operation with the correct voltages on its CC pins.

Copyright © 2016, Texas Instruments Incorporated

Once this process has occurred, the TPS65982 can start negotiating with the power adaptor through USB PD for higher power levels, allowing 100-W operation in dead battery mode.

For more information on the TPD8S300 dead battery operation, see the *CC Dead Battery Resistors Integrated for Handling the Dead Battery Use Case in Mobile Devices* section in the description section of the datasheet. Also, see 図 32 for a waveform of the CC line when the TPD8S300 is turning on and exposing the TPS65982s dead battery resistors to the USB Type-C connector.

9.2.2.3 CC Line Capacitance

USB PD has a specification for the total amount of capacitance that is required for proper USB PD BMC operation on the CC lines. The specification from section 5.8.6 of the USB PD Specification is given below in 表 4.

表 4. USB PD cReceiver Specification

NAME	DESCRIPTION	MIN	MAX	UNIT	COMMENT
cReceiver	CC receiver capacitance	200	600	pF	The DFP or UFP system shall have capacitance within this range when not transmitting on the line.

Therefore, the capacitance on the CC lines must stay in between 200 pF and 600 pF when USB PD is being used. Therefore, the combination of capacitances added to the system by the TPS65982, the TPD8S300, and any external capacitor must fall within these limits. 表 5 shows the analysis involved in choosing the correct external CC capacitor for this system, and shows that an external CC capacitor is required.

表 5. CC Line Capacitor Calculation

CC Capacitance	MIN	MAX	UNIT	COMMENT
CC line target capacitance	200	600	pF	From the *USB PD Specification* section (cReceiver, section 5.8.6).
TPS65982 capacitance	70	120	pF	From the TPS65982 Datasheet.
TPD8S300 capacitance	60	120	pF	From the *Electrical Characteristics* table.
Proposed capacitor GRM033R71E221KA01D	110	330	pF	CAP, CERM, 220 pF, 25 V, ±10%, X7R, 0201 (For min and max, assume ±50% capacitance change with temperature and voltage derating to be overly conservative).
TPS65982 + TPD8S300 + GRM033R71E221KA01D	240	570	pF	Meets USB PD cReceiver Specification

9.2.2.4 Additional ESD Protection on CC and SBU Lines

If additional IEC ESD protection is desired to be placed on either the CC or SBU lines, it is important that high-voltage ESD protection diodes be used. The maximum DC voltage that can be seen in USB PD is 21-V_{BUS}, with 21.5 V allowed during voltage transitions. Therefore, an ESD protection diode must have a reverse stand off voltage higher than 21.5 V in order to guarantee the diode does not breakdown during a short-to-V_{BUS} event and have large amounts of current flowing through it indefinitely, destroying the diode. A reverse stand off voltage of 24 V is recommended to give margin above 21.5 V in case USB Type-C power adaptors are released in the market which break the USB Type-C specification.

Furthermore, due to the fact that the Short-to-V_{BUS} event applies a DC voltage to the CC and SBU pins, a deep-snap back diode cannot be used unless its minimum trigger voltage is above 42 V. During a Short-to-V_{BUS} event, RLC ringing of up to 2x the settling voltage can be exposed to CC and SBU, allowing for up to 42 V to be exposed. Furthermore, if any capacitor derates on the CC or SBU line, greater than 2x ringing can occur. Since this ringing is hard to bound, it is recommended to not use deep-snap back diodes. If the diode triggers during the short-to-V_{BUS} hot-plug event, it begins to operate in is conduction region. With a 20-V_{BUS} source present on the CC or SBU line, this allows the diode to conduct indefinitely, destroying the diode.

9.2.2.5 $\overline{FLT}$ Pin Operation

The $\overline{FLT}$ and OVP FET have specific timing parameters to allow different benefits depending on how the system designer desires the system to respond to a Short-to-V_{BUS} event.

Copyright © 2016, Texas Instruments Incorporated

Once a Short-to-V_{BUS} occurs on the C_CCx or C_SBUx pins, the $\overline{FLT}$ pin is asserted in 20 µs (typical) so the PD controller can be notified quickly. If V_{BUS} is being shorted to CC or SBU, it is recommended to respond to the event by forcing a detach in the USB PD controller to remove V_{BUS} from the port. Although the USB Type-C port using the TPD8S300 is not damaged, as the TPD8S300 provides protection from these events, the other device connected through the USB Type-C Cable or any active circuitry in the cable can be damaged. Although shutting the V_{BUS} off through a detach does not guarantee it stops the other device or cable from being damaged, it can mitigate any high current paths from causing further damage after the initial damage takes place. Additionally, even if the active cable or other device does have proper protection, the short-to-V_{BUS} event may corrupt a configuration in an active cable or in the other PD controller, so it is best to detach and reconfigure the port.

For UFPs, the TPD8S300 automatically forces a detach, removing the need to use the $\overline{FLT}$ pin if the only response required by your system during a short-to-V_{BUS} event is forcing a detach on the port. The TPD8S300 keeps its CC OVP FET OFF for at least 21 ms after a Short-to-V_{BUS} event occurs, causing the CC line voltage to change from is configuration value for more than 20 ms, forcing the PD controllers to detach. For DFPs, this operation cannot be guaranteed because of the parasitic diode in the OVP FET from CCx to C_CCx and from SBUx to C_SBUx. Therefore for DFPs, using the $\overline{FLT}$ pin recommended. For our application using the TPS65982 as a DRP, using the $\overline{FLT}$ pin is recommended.

9.2.2.6 How to Connect Unused Pins

If either the RPD_Gx pins or any of the Dx pins are unused in a design, they must be connected to GND.

9.2.3 Application Curves

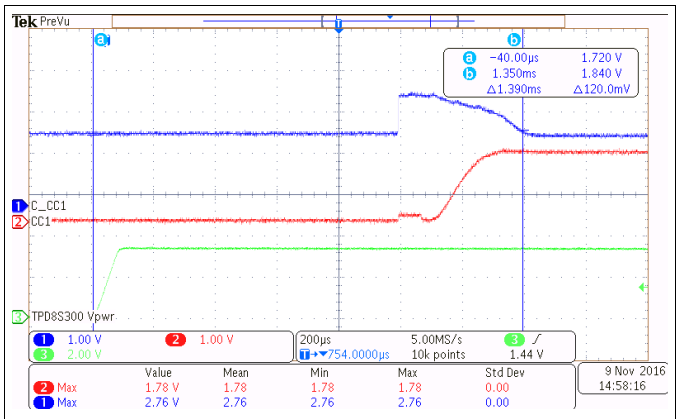


図 32. TPD8S300 and TPS65982 Turning On in Dead Battery Mode

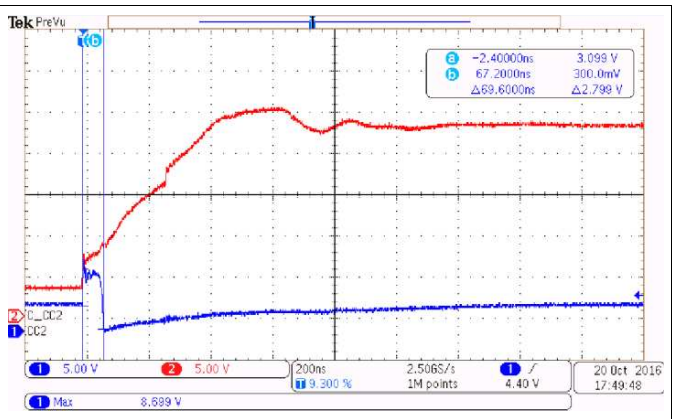


図 33. TPD8S300 Protecting the TPS65982 During a Short-to-V_{BUS} Event

Copyright © 2016, Texas Instruments Incorporated

10 Power Supply Recommendations

The VPWR pin provides power to all the circuitry in the TPD8S300. It is recommended a 1-µF decoupling capacitor is placed as close as possible to the VPWR pin. If USB PD is desired to be operated in dead battery conditions, it is critical that the TPD8S300 share the same power supply as the PD controller in dead battery boot-up (such as sharing the same dead battery LDO). See the *CC Dead Battery Resistors Integrated for Handling the Dead Battery Use Case in Mobile Devices* section for more details.

Copyright © 2016, Texas Instruments Incorporated

11 Layout

11.1 Layout Guidelines

Proper routing and placement is important to maintain the signal integrity the USB2.0, SBU, CC line signals. The following guidelines apply to the TPD8S300:

- Place the bypass capacitors as close as possible to the V_{PWR} pin, and ESD protection capacitor as close as possible to the V_{BIAS} pin. Capacitors must be attached to a solid ground. This minimizes voltage disturbances during transient events such as short-to-V_{BUS} and ESD strikes.
- The USB2.0 and SBU lines must be routed as straight as possible and any sharp bends must be minimized.

Standard ESD recommendations apply to the C_CC1, C_CC2, C_SBU1, C_SBU2, D1, D2, D3, and D4 pins as well:

- The optimum placement for the device is as close to the connector as possible:
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TPD8S300 and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.
- It is best practice to not via up to the D1, D2, D3, and D4 pins from a trace routed on another layer. Rather, it is better to via the trace to the layer with the Dx pin, and to continue that trace on that same layer. See the *ESD Protection Layout Guide* application report, section 1.3 for more details.

11.2 Layout Example

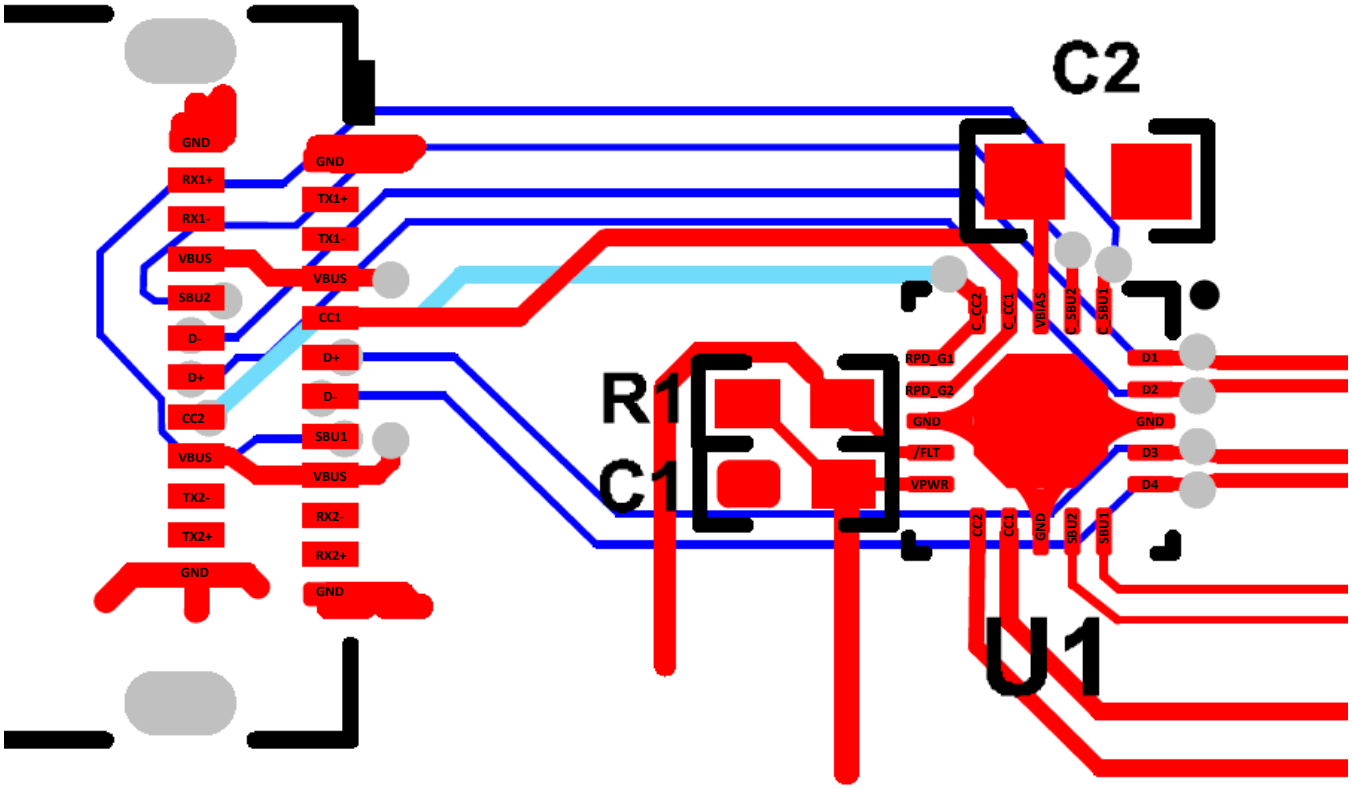


図 34. TPD8S300 Typical Layout

Copyright © 2016, Texas Instruments Incorporated

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

関連資料については、以下を参照してください。

『TPD8S300評価モジュール・ユーザー・ガイド』

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™オンライン・コミュニティ ***TIのE2E（Engineer-to-Engineer）コミュニティ。*** エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイディアを検討して、問題解決に役立てることができます。

設計サポート ***TIの設計サポート*** 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.4 商標

E2E is a trademark of Texas Instruments.
USB Type-C is a trademark of USB Implementers Forum.
All other trademarks are the property of their respective owners.

12.5 静電気放電に関する注意事項

これらのデバイスは、限定的なESD（静電破壊）保護機能を内 蔵しています。保存時または取り扱い時は、MOSゲートに対す る静電破壊を防止するために、リード線同士をショートさせて おくか、デバイスを導電フォームに入れる必要があります。

12.6 用語集

SLYZ022 — *TI用語集*.

この用語集には、用語や略語の一覧および定義が記載されています。

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPD8S300RUKR	Active	Production	WQFN (RUK) | 20	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8S30
TPD8S300RUKR.A	Active	Production	WQFN (RUK) | 20	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8S30
TPD8S300RUKRG4	Active	Production	WQFN (RUK) | 20	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8S30
TPD8S300RUKRG4.A	Active	Production	WQFN (RUK) | 20	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8S30

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

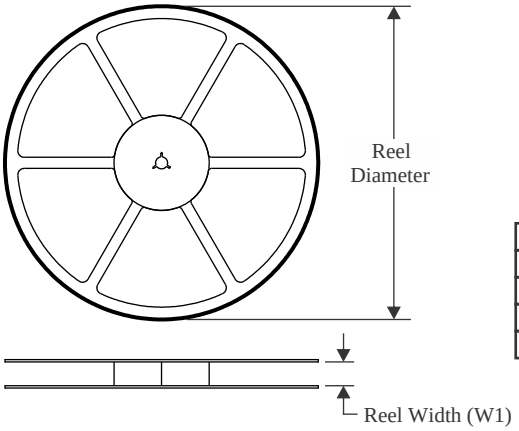
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

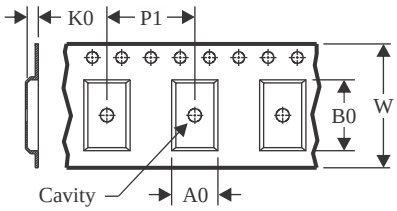
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

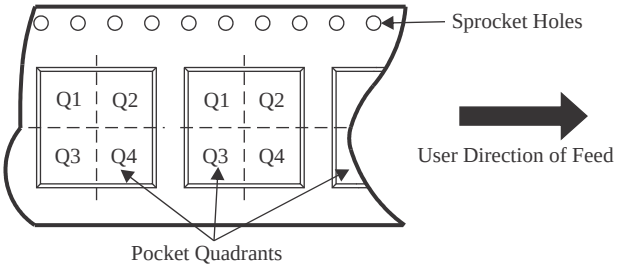


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

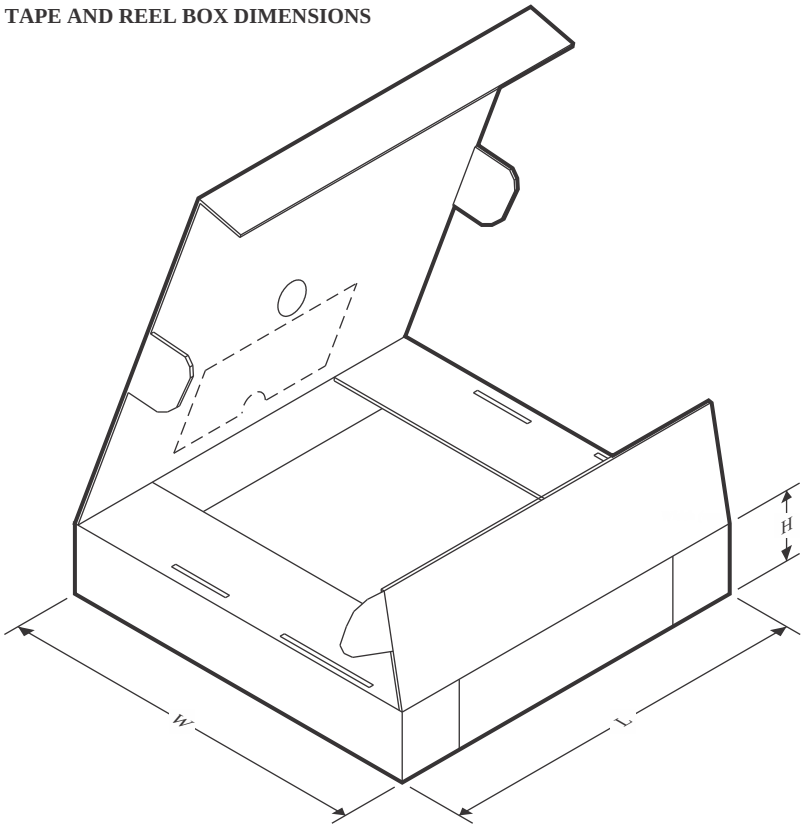
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD8S300RUKR	WQFN	RUK	20	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPD8S300RUKR	WQFN	RUK	20	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPD8S300RUKRG4	WQFN	RUK	20	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD8S300RUKR	WQFN	RUK	20	3000	360.0	360.0	36.0
TPD8S300RUKR	WQFN	RUK	20	3000	346.0	346.0	33.0
TPD8S300RUKRG4	WQFN	RUK	20	3000	346.0	346.0	33.0

GENERIC PACKAGE VIEW

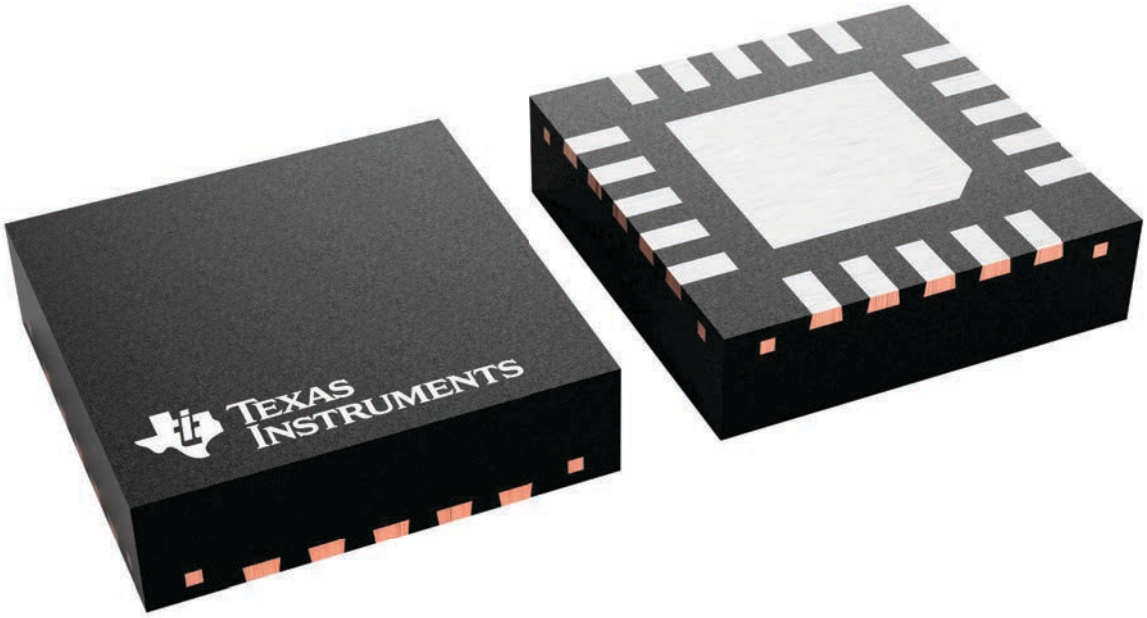
RUK 20

WQFN - 0.8 mm max height

3 x 3, 0.4 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



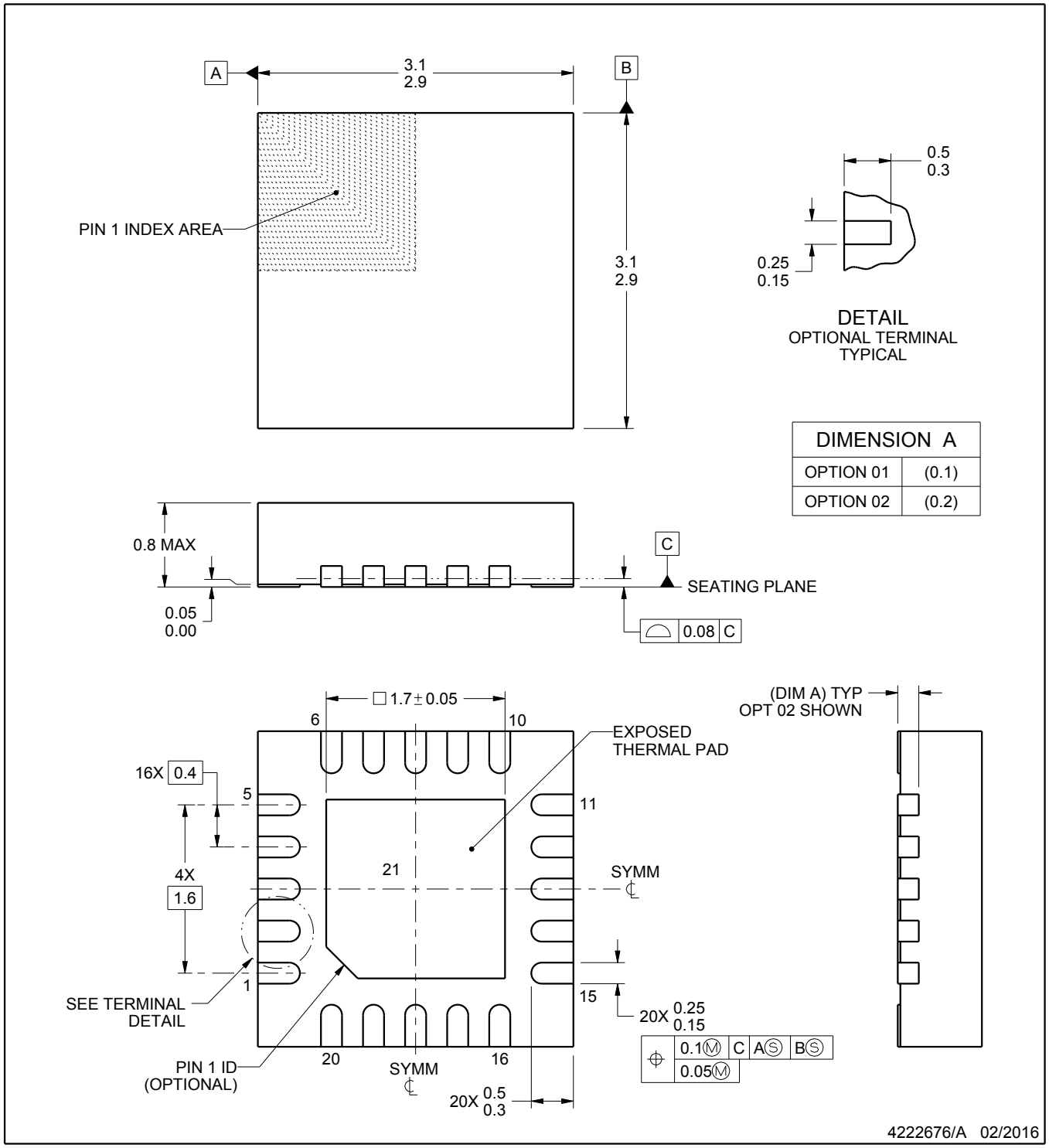
4229651/A

PACKAGE OUTLINE

RUK0020B

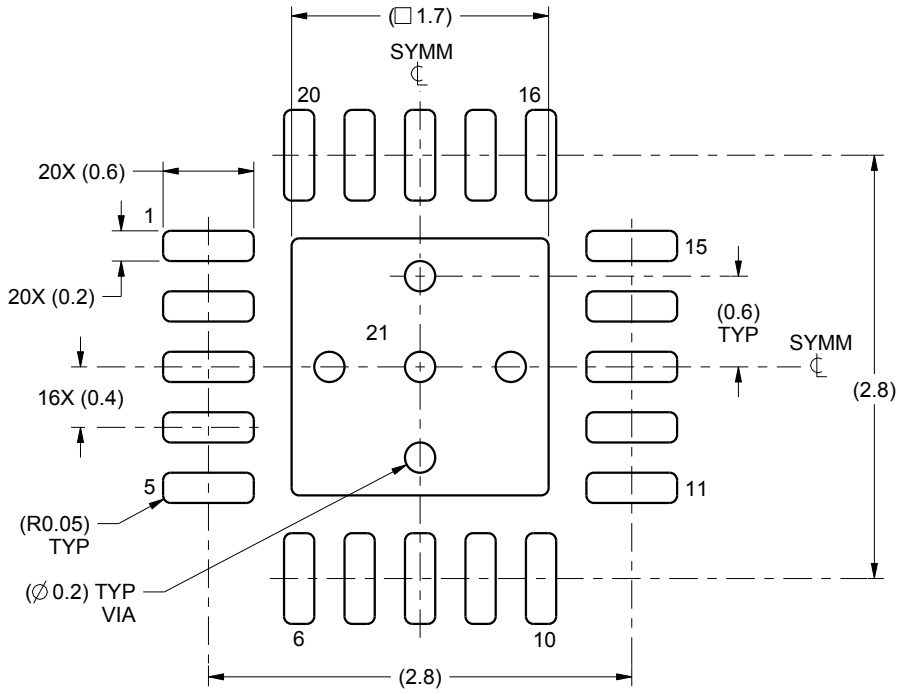
WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

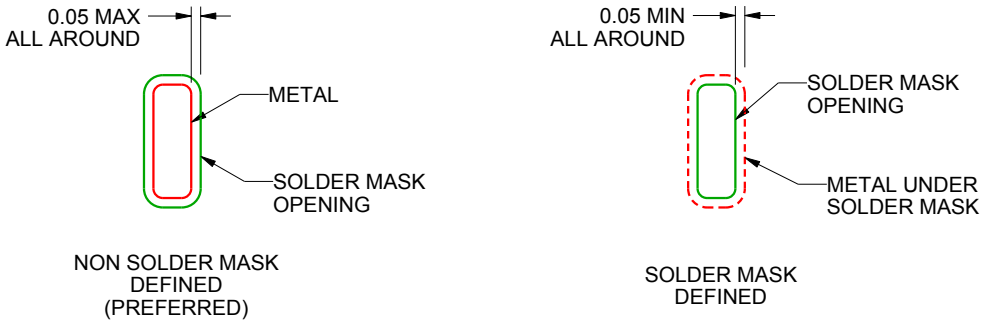


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:20X

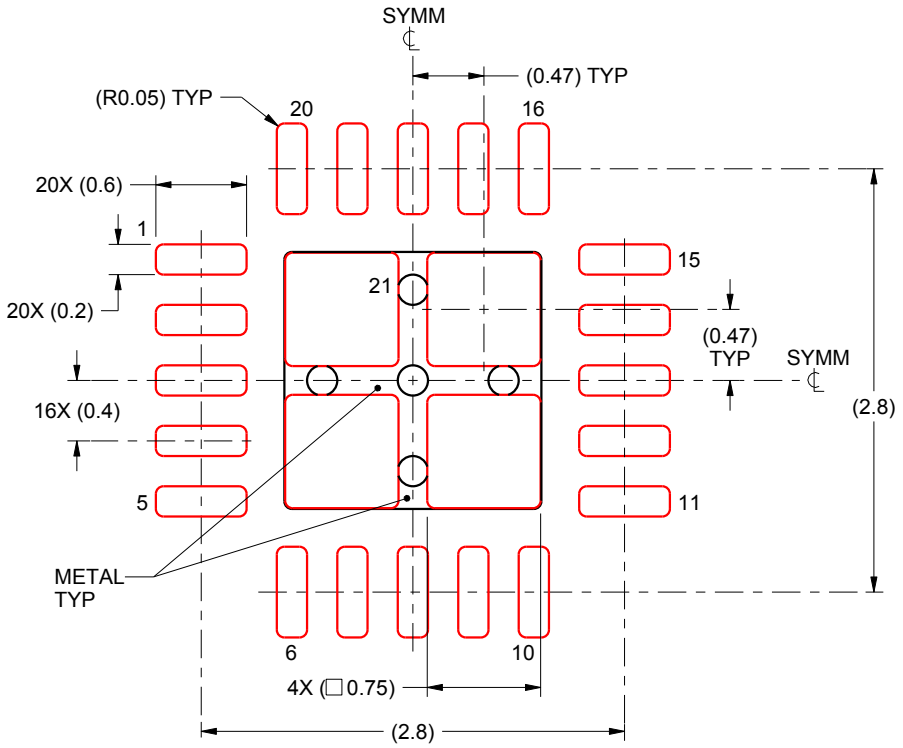


SOLDER MASK DETAILS

4222676/A 02/2016

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL

EXPOSED PAD 21:
78% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:20X

4222676/A 02/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要なお知らせと免責事項

TI は、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、 TI の販売条件 、 TI の総合的な品質ガイドライン 、 ti.com または TI 製品などに関連して提供される他の適用条件に従い提供されます。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。 TI がカスタム、またはカスタマー仕様として明示的に指定していない限り、TI の製品は標準的なカタログに掲載される汎用機器です。

お客様がいかなる追加条項または代替条項を提案する場合も、TI はそれらに異議を唱え、拒否します。

Copyright © 2026, Texas Instruments Incorporated

最終更新日：2025 年 10 月